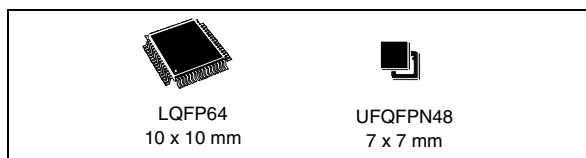


Ultralow power 32-bit MCU ARM®-based Cortex™-M3,
128KB Flash, 10KB SRAM, 2KB EEPROM, LCD, USB, ADC, DAC

Datasheet – preliminary data



Features

- Ultralow power platform
 - 1.8 V to 3.6 V power supply
 - -40°C to 85°C temperature range
 - 0.3 µA Standby mode (3 wakeup pins)
 - 0.9 µA Standby mode + RTC
 - 0.57 µA Stop mode (16 wakeup lines)
 - 1.2 µA Stop mode + RTC
 - 9 µA Low-power Run mode
 - 214 µA/MHz Run mode
 - 10 nA ultra-low I/O leakage
 - < 8 µs wakeup time
- Core: ARM 32-bit Cortex™-M3 CPU
 - From 32 kHz up to 32 MHz max
 - 33.3 DMIPS peak (Dhrystone 2.1)
 - Memory protection unit
- Reset and supply management
 - Ultrasafe, low power BOR (brownout reset) with 5 selectable thresholds
 - Ultralow power POR/PDR
 - Programmable voltage detector (PVD)
- Clock sources
 - 1 to 24 MHz crystal oscillator
 - 32 kHz oscillator for RTC with calibration
 - High Speed Internal 16 MHz
 - Internal Low Power 37 kHz RC
 - Internal multispeed low power 65 kHz to 4.2 MHz
 - PLL for CPU clock and USB (48 MHz)
- Pre-programmed bootloader
 - USART supported
- Development support
 - Serial wire debug supported
 - JTAG supported
- Up to 51 fast I/Os (42 I/Os 5V tolerant), all mappable on 16 external interrupt vectors
- Memories
 - Up to 128 KB Flash with ECC
 - Up to 10 KB RAM
 - Up to 2 KB of true EEPROM with ECC
 - 20 Byte Backup Register
- LCD Driver for up to 8x28 segments
- Analog peripherals
 - 12-bit ADC 1 Msps up to 20 channels
 - 12-bit DAC 2 channels with output buffers
 - Two ultralow power comparators
- Seven DMA controller channels
- Eight communication interface peripherals
 - One USB 2.0
 - Three USART (ISO 7816, IrDA)
 - Two SPI (16 Mbits/s)
 - Two I2C (SMBus/PMBus)
- Ten timers:
 - Six 16-bit timers with up to 4 IC/OC/PWM channels
 - Two 16-bit basic timers
 - Two watchdog timers (independent and window)
- CRC calculation unit

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1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32L100C6 and STM32L100R8/B ultralow power ARM® Cortex™-based microcontrollers product line.

The ultralow power STM32L100xx⁽¹⁾ family includes devices in 2 different package types: 48 or 64 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultralow power STM32L100xx microcontroller family suitable for a wide range of applications:

- Medical and handheld equipment
- Application control and user interface
- PC peripherals, gaming, GPS and sport equipment
- Alarm systems, Wired and wireless sensors, Video intercom
- Utility metering

This STM32L100C6 and STM32L100R8/B datasheet should be read in conjunction with the STM32L1xxx reference manual (RM0038).

The document "Getting started with STM32L1xxx hardware development" AN3216 gives a hardware implementation overview. The both documents are available from the STMicroelectronics website www.st.com.

For information on the Cortex™-M3 core please refer to the Cortex™-M3 Technical Reference Manual, available from the www.arm.com website at the following address: <http://infocenter.arm.com/help/index.jsp?topic=/com.arm.doc.ddi0337g>.

Figure 1 shows the general block diagram of the device family.

1. In this document, STM32L100xx refers to STM32L100C6, STM32L100R8 and STM32L100RB.

2 Description

The ultralow power STM32L100xx incorporates the connectivity power of the universal serial bus (USB) with the high-performance ARM Cortex™-M3 32-bit RISC core operating at a 32 MHz frequency, a memory protection unit (MPU), high-speed embedded memories (Flash memory up to 128 Kbytes and RAM up to 10 Kbytes) and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

All devices offer a 12-bit ADC, 2 DACs and 2 ultralow power comparators, six general-purpose 16-bit timers and two basic timers, which can be used as time bases.

Moreover, the STM32L100xx devices contain standard and advanced communication interfaces: up to two I²Cs and SPIs, three USARTs and a USB.

They also include a real-time clock and a set of backup registers that remain powered in Standby mode.

Finally, the integrated LCD controller has a built-in LCD voltage generator that allows you to drive up to 8 multiplexed LCDs with contrast independent of the supply voltage.

The ultralow power STM32L100xx operates from a 1.8 to 3.6 V power supply (down to 1.65 V at power down). It is available in the -40 to +85 °C temperature range. A comprehensive set of power-saving modes allows the design of low-power applications.



2.1 Device overview

Table 1. Ultralow power STM32L100xx device features and peripheral counts

Peripheral		STM32L100C6	STM32L100R8/B	
Flash (Kbytes)		32	64	128
Data EEPROM (Kbytes)		2		
RAM (Kbytes)		4	8	10
Timers	General-purpose	6		
	Basic	2		
Communication interfaces	SPI	2		
	I ² C	2		
	USART	3		
	USB	1		
GPIOs		37	51	
12-bit synchronized ADC Number of channels		1 16 channels	1 20 channels	
12-bit DAC Number of channels		2 2		
LCD COM x SEG		4x16	4x32 8x28	
Comparator		2		
Max. CPU frequency		32 MHz		
Operating voltage		1.8 V to 3.6 V		
Operating temperatures		Ambient temperatures: −40 to +85 °C Junction temperature: −40 to + 105 °C		
Packages		UFQFPN48	LQFP64	

2.2 Ultralow power device continuum

The ultralow power STM32L100C6 and STM32L100R8/B are fully pin-to-pin and software compatible. Besides the full compatibility within the family, the devices are part of STMicroelectronics microcontrollers ultralow power strategy which also includes STM8L1xx and STM8L0xx devices. The STM8L and STM32L families allow a continuum of performance, peripherals, system architecture and features.

They are all based on STMicroelectronics ultralow leakage process.

Note: The ultralow power STM32L and general-purpose STM32Fxxx families are pin-to-pin compatible. The STM8L15xxx devices are pin-to-pin compatible with the STM8L101xx devices. Please refer to the STM32F and STM8L documentation for more information on these devices.

2.2.1 Performance

All families incorporate highly energy-efficient cores with both Harvard architecture and pipelined execution: advanced STM8 core for STM8L families and ARM Cortex™-M3 core for STM32L family. In addition specific care for the design architecture has been taken to optimize the mA/DMIPS and mA/MHz ratios.

This allows the ultralow power performance to range from 5 up to 33.3 DMIPs.

2.2.2 Shared peripherals

STM8L15xxx and STM32L1xxxx share identical peripherals which ensure a very easy migration from one family to another:

- Analog peripherals: ADC, DAC and comparators
- Digital peripherals: RTC and some communication interfaces

2.2.3 Common system strategy

To offer flexibility and optimize performance, the STM8L15xx and STM32L1xxxx families use a common architecture:

- Same power supply range from 1.8 V to 3.6 V
- Architecture optimized to reach ultralow consumption both in low power modes and Run mode
- Fast startup strategy from low power modes
- Flexible system clock
- Ultrasafe reset: same reset strategy including power-on reset, power-down reset, brownout reset and programmable voltage detector.

2.2.4 Features

ST ultralow power continuum also lies in feature compatibility:

- More than 10 packages with pin count from 20 to 144 pins and size down to 3 x 3 mm
- Memory density ranging from 4 to 384 Kbytes

Figure 1 shows the block diagrams.

The block diagram illustrates the internal architecture of the STM32F405VGT6 microcontroller. Key components include:

- Cortex-M3 CPU:** Features JTAG & SW, NVIC, and GP DMA (7 channels) connected via a Bus Matrix.
- Power Management:** Includes a VOLT. REG. block with VDD (1.8 V to 3.6 V) and VSS pins, and a VDDA pin for the PLL & clock management block.
- Clock Management:** Features a PLL & clock management block connected to XTAL OSC (1-24 MHz) and various clock outputs (AHBP CLK, APBP CLK, HCLK, FCLK).
- Flash Memory:** 128 KB Flash and 2 KB data EEPROM.
- RAM:** 10 KB RAM.
- GPIOs:** PA[15:0], PB[15:0], PC[15:0], and PD2.
- Timers:** TIM2, TIM3, TIM4, TIM9, TIM10, TIM11, TIM6, and TIM7.
- Serial Interfaces:** USART 2, USART 3, SPI1, SPI2, I2C 1, and I2C 2.
- Other Peripherals:** IWDG, RTC, Backup register, LCD step-up converter, and USB 2.0 FS device.
- Power Pins:** VDD, VSS, VDDA, VDDP, and VREF.
- Signal Pins:** NJT RST, JT DI, JT CK/SWCLK, JTMS/JWDAT, JTDO as AF, NRST, VREF OUTPUT, COMP2_IN-/IN+, PA[15:0], PB[15:0], PC[15:0], PD2, 51AF, MOSI_MISO, SCK_NSS as AF, RX,TX,CTS,RTS,SmartCard as AF, 20AF, VDDREF_ADC, VSSREF_ADC, OSC32_IN, OSC32_OUT, RTC_AFIN, RTC_OUT, RTC_TS,RTC_TAMP, V_LCD, RX,TX,CTS,RTS,SmartCard as AF, MOSI,MISO,SCK,NSS as AF, SCL,SDA as AF, SCL,SDA,SMBus,PMBus as AF, USB_DP, USB_DM, SEG x, COM x, DAC_OUT1 as AF, and DAC_OUT2 as AF.

3.1 Low power modes

The ultralow power STM32L100xx supports dynamic voltage scaling to optimize its power consumption in run mode. The voltage from the internal low-drop regulator that supplies the logic can be adjusted according to the system's maximum operating frequency and the external voltage supply:

- In range 1 (V_{DD} range limited to 2.0-3.6 V), the CPU runs at up to 32 MHz (refer to [Table 15](#) for consumption).
- In range 2 (full V_{DD} range), the CPU runs at up to 16 MHz (refer to [Table 15](#) for consumption)
- In range 3 (full V_{DD} range), the CPU runs at up to 4 MHz (generated only with the multispeed internal RC oscillator clock source). Refer to [Table 15](#) for consumption.

Seven low power modes are provided to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep mode**
In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.
Sleep mode power consumption: refer to [Table 17](#).
- **Low power run mode**
This mode is achieved with the multispeed internal (MSI) RC oscillator set to the minimum clock (65 kHz), execution from SRAM or Flash memory, and internal regulator in low power mode to minimize the regulator's operating current. In the Low power run mode, the clock frequency and the number of enabled peripherals are both limited.
Low power run mode consumption: refer to [Table 18: Current consumption in Low power run mode](#).
- **Low power sleep mode**
This mode is achieved by entering the Sleep mode with the internal voltage regulator in Low power mode to minimize the regulator's operating current. In the Low power sleep mode, both the clock frequency and the number of enabled peripherals are limited; a typical example would be to have a timer running at 32 kHz.
When wakeup is triggered by an event or an interrupt, the system reverts to the run mode with the regulator on.
Low power sleep mode consumption: refer to [Table 19: Current consumption in Low power sleep mode](#).
- **Stop mode with RTC**
Stop mode achieves the lowest power consumption while retaining the RAM and register contents and real time clock. All clocks in the V_{CORE} domain are stopped, the PLL, MSI RC, HSI RC and HSE crystal oscillators are disabled. The LSE or LSI is still running. The voltage regulator is in the low power mode.
The device can be woken up from Stop mode by any of the EXTI line, in 8 μ s. The EXTI line source can be one of the 16 external lines. It can be the PVD output, the Comparator 1 event or Comparator 2 event (if internal reference voltage is on), it can be the RTC alarm(s), the USB wakeup, the RTC tamper events, the RTC timestamp event or the RTC wakeup.
- **Stop mode without RTC**
Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, LSE and

HSE crystal oscillators are disabled. The voltage regulator is in the low power mode. The device can be woken up from Stop mode by any of the EXTI line, in 8 μ s. The EXTI line source can be one of the 16 external lines. It can be the PVD output, the Comparator 1 event or Comparator 2 event (if internal reference voltage is on). It can also be wakened by the USB wakeup.

Stop mode consumption: refer to [Table 20: Typical and maximum current consumptions in Stop mode](#).

- **Standby mode with RTC**

Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI RC and HSE crystal oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC_CSR).

The device exits Standby mode in 60 μ s when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.

- **Standby mode without RTC**

Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI, RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC_CSR).

The device exits Standby mode in 60 μ s when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

Standby mode consumption: refer to [Table 21](#).

Note: *The RTC, the IWDG, and the corresponding clock sources are not stopped by entering the Stop or Standby mode.*

Table 2. Functionalities depending on the operating power supply range

Operating power supply range	Functionalities depending on the operating power supply range			
	DAC and ADC operation	USB	Dynamic voltage scaling range	I/O operation
$V_{DD} = 1.8$ to 2.0 V	Conversion time up to 500 Ksps	Not functional	Range 2 or range 3	Degraded speed performance
$V_{DD} = 2.0$ to 2.4 V	Conversion time up to 500 Ksps	Functional ⁽¹⁾	Range 1, range 2 or range 3	Full speed operation
$V_{DD} = 2.4$ to 3.6 V	Conversion time up to 1 Msps	Functional ⁽¹⁾	Range 1, range 2 or range 3	Full speed operation

1. Should be USB compliant from I/O voltage standpoint, the minimum V_{DD} is 3.0 V.

Table 3. CPU frequency range depending on dynamic voltage scaling

CPU frequency range	Dynamic voltage scaling range
16 MHz to 32 MHz (1ws) 32 kHz to 16 MHz (0ws)	Range 1
8 MHz to 16 MHz (1ws) 32 kHz to 8 MHz (0ws)	Range 2
2.1 MHz to 4.2 MHz (1ws) 32 kHz to 2.1 MHz (0ws)	Range 3

Table 4. Working mode-dependent functionalities (from Run/active down to standby)

Ips	Run/Active	Sleep	Low-power Run	Low-power Sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
CPU	Y	--	Y	--	--		--	
Flash	Y	Y	Y	N	--		--	
RAM	Y	Y	Y	Y	Y		--	
Backup Registers	Y	Y	Y	Y	Y		Y	
EEPROM	Y	--	Y	Y	Y		--	
Brown-out rest (BOR)	Y	Y	Y	Y	Y	Y	Y	
DMA	Y	Y	Y	Y	--		--	
Programmable Voltage Detector (PVD)	Y	Y	Y	Y	Y	Y	Y	
Power On Reset (POR)	Y	Y	Y	Y	Y	Y	Y	
Power Down Rest (PDR)	Y	Y	Y	Y	Y		Y	
High Speed Internal (HSI)	Y	Y	--	--	--		--	
High Speed External (HSE)	Y	Y	--	--	--		--	
Low Speed Internal (LSI)	Y	Y	Y	Y	Y		--	
Low Speed External (LSE)	Y	Y	Y	Y	Y		--	
Multi-Speed Internal (MSI)	Y	Y	Y	Y	--		--	
Inter-Connect Controller	Y	Y	Y	Y	--		--	
RTC	Y	Y	Y	Y	Y	Y	Y	
RTC Tamper	Y	Y	Y	Y	Y	Y	Y	Y
Auto WakeUp (AWU)	Y	Y	Y	Y	Y	Y	Y	Y
LCD	Y	Y	Y	Y	Y		--	
USB	Y	Y	--	--	--	Y	--	
USART	Y	Y	Y	Y	Y	(1)	--	
SPI	Y	Y	Y	Y			--	
I2C	Y	Y	Y	Y		(1)	--	
ADC	Y	Y	--	--	--		--	

Table 4. Working mode-dependent functionalities (from Run/active down to standby) (continued)

Ips	Run/Active	Sleep	Low-power Run	Low-power Sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
DAC	Y	Y	Y	Y	Y		--	
Comparators	Y	Y	Y	Y	Y	Y	--	
16-bit and 32-bit Timers	Y	Y	Y	Y	--		--	
IWDG	Y	Y	Y	Y	Y	Y	Y	Y
WWDG	Y	Y	Y	Y	--		--	
Systic Timer	Y	Y	Y	Y			--	
GPIOs	Y	Y	Y	Y	Y	Y		3 Pins
Wakeup time to Run mode	0 μ s	0.36 μ s	3 μ s	32 μ s	< 8 μ s		50 μ s	
Consumption V_{DD} =1.8V to 3.6V (Typ)	Down to 214 μ A/MHz (from Flash)	Down to 50 μ A/MHz (from Flash)	Down to 9 μ A	Down to 4.4 μ A	0.65 μ A (No RTC) V_{DD} =1.8V		0.3 μ A (No RTC) V_{DD} =1.8V	
					1.4 μ A (with RTC) V_{DD} =1.8V		1 μ A (with RTC) V_{DD} =1.8V	
					0.65 μ A (No RTC) V_{DD} =3.0V		0.3 μ A (No RTC) V_{DD} =3.0V	
					1.6 μ A (with RTC) V_{DD} =3.0V		1.3 μ A (with RTC) V_{DD} =3.0V	

1. The startup on communication line wakes the CPU which was made possible by an EXTI, this induces a delay before entering run mode.

3.2 ARM[®] Cortex[™]-M3 core with MPU

The ARM Cortex[™]-M3 processor is the industry leading processor for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM Cortex[™]-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

The memory protection unit (MPU) improves system reliability by defining the memory attributes (such as read/write access permissions) for different memory regions. It provides up to eight different regions and an optional predefined background region.

Owing to its embedded ARM core, the STM32L100xx is compatible with all ARM tools and software.

Nested vectored interrupt controller (NVIC)

The ultralow power STM32L100xx embeds a nested vectored interrupt controller able to handle up to 45 maskable interrupt channels (not including the 16 interrupt lines of Cortex™-M3) and 16 priority levels.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of *late arriving*, higher-priority interrupts
- Support for tail-chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.

3.3 Reset and supply management

3.3.1 Power supply schemes

- $V_{DD} = 1.8$ to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA} , $V_{DDA} = 1.8$ to 3.6 V: external analog power supplies for ADC, reset blocks, RCs and PLL.
 V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS} , respectively.

3.3.2 Power supply supervisor

The device has an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

BOR is activated at power-on and the device operate between 1.8 V and 3.6 V.

After the V_{DD} threshold is reached, the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently: in this case, the V_{DD} min value becomes 1.65 V.

BOR ensures proper operation starting from 1.8 V whatever the power ramp-up phase before it reaches 1.8 V.

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage (V_{REFINT}) in Stop mode. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for any external reset circuit.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.3.3 Voltage regulator

The regulator has three operation modes: main (MR), low power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low-power run, Low-power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost except for the standby circuitry (wake-up logic, IWDG, RTC, LSI, LSE crystal 32K osc, RCC_CSR).

3.3.4 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from Flash memory
- Boot from System Memory
- Boot from embedded RAM

The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART1 or USART2. See STM32™ microcontroller system memory boot mode AN2606 for details. The HSI oscillator is to be calibrated to +/-1% before using of the bootloader.

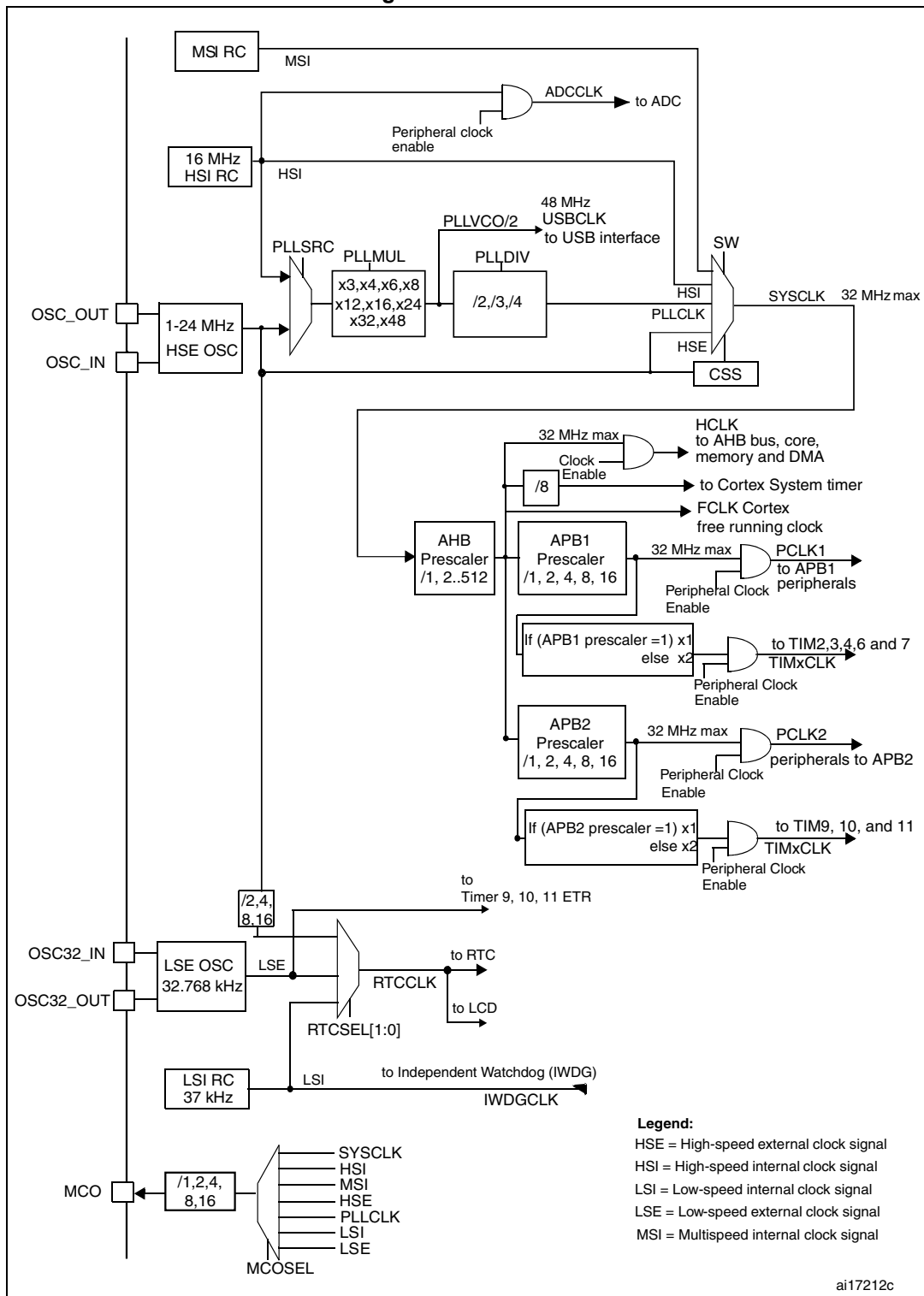
3.4 Clock management

The clock controller distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low power modes and ensures clock robustness. It features:

- **Clock prescaler:** to get the best tradeoff between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler
- **Safe clock switching:** clock sources can be changed safely on the fly in run mode through a configuration register.
- **Clock management:** to reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.
- **Master clock source:** three different clock sources can be used to drive the master clock:
 - 1-24 MHz high-speed external crystal (HSE), that can supply a PLL
 - 16 MHz high-speed internal RC oscillator (HSI), trimmable by software, that can supply a PLL
 - Multispeed internal RC oscillator (MSI), trimmable by software, able to generate 7 frequencies (65.5 kHz, 131 kHz, 262 kHz, 524 kHz, 1.05 MHz, 2.1 MHz, 4.2 MHz) with a consumption proportional to speed, down to 750 nA typical. When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be trimmed by software down to a $\pm 0.5\%$ accuracy.
- **Auxiliary clock source:** two ultralow power clock sources that can be used to drive the LCD controller and the real-time clock:
 - 32.768 kHz low-speed external crystal (LSE)
 - 37 kHz low-speed internal RC (LSI), also used to drive the independent watchdog. The LSI clock can be measured using the high-speed internal RC oscillator for greater precision.
- **RTC and LCD clock sources:** the LSI, LSE or HSE sources can be chosen to clock the RTC and the LCD, whatever the system clock.
- **USB clock source:** the embedded PLL has a dedicated 48 MHz clock output to supply the USB interface.
- **Startup clock:** after reset, the microcontroller restarts by default with an internal 2.1 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.
- **Clock security system (CSS):** this feature can be enabled by software. If a HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled.
- **Clock-out capability (MCO: microcontroller clock output):** it outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See [Figure 2](#) for details on the clock tree.

Figure 2. Clock tree



1. For the USB function to be available, both HSE and PLL must be enabled, with the CPU running at either 24 MHz or 32 MHz.

3.5 Low power real-time clock and backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the second, minute, hour (12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are made automatically. The RTC provides a programmable alarm and programmable periodic interrupts with wakeup from Stop and Standby modes.

- The programmable wakeup time ranges from 120 μ s to 36 hours
- Stop mode consumption with LSI and Auto-wakeup: 1.2 μ A (at 1.8 V) and 1.4 μ A (at 3.0 V)
- Stop mode consumption with LSE, calendar and Auto-wakeup: 1.3 μ A (at 1.8V), 1.6 μ A (at 3.0 V)

The RTC can be calibrated with an external 512 Hz output, and a digital compensation circuit helps reduce drift due to crystal deviation.

There are twenty 32-bit backup registers provided to store 20 bytes of user application data. They are cleared in case of tamper detection.

3.6 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated AFIO registers. All GPIOs are high current capable. The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to the AHB with a toggling speed of up to 16 MHz.

External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 23 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 51 GPIOs can be connected to the 16 external interrupt lines. The 7 other lines are connected to RTC, PVD, USB or Comparator events.

3.7 Memories

The STM32L100xx devices have the following features:

- Up to 10 Kbyte of embedded RAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
 - 32, 64 or 128 Kbyte of embedded Flash program memory
 - 2 Kbyte of data EEPROM
 - Options bytes

The options bytes are used to write-protect the memory (with 4 KB granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no readout protection
- Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- Level 2: chip readout protection, debug features (Cortex-M3 JTAG and serial wire) and boot in RAM selection disabled (JTAG fuse)

The whole non-volatile memory embeds the error correction code (ECC) feature.

3.8 DMA (direct memory access)

The flexible 7-channel, general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I²C, USART, general-purpose timers and ADC.

3.9 LCD (liquid crystal display)

The LCD drives up to 8 common terminals and 32 segment terminals to drive up to 224 pixels.

- Internal step-up converter to guarantee functionality and contrast control irrespective of V_{DD} . This converter can be deactivated, in which case the V_{LCD} pin is used to provide the voltage to the LCD
- Supports static, 1/2, 1/3, 1/4 and 1/8 duty
- Supports static, 1/2, 1/3 and 1/4 bias
- Phase inversion to reduce power consumption and EMI
- Up to 8 pixels can be programmed to blink
- Unneeded segments and common pins can be used as general I/O pins
- LCD RAM can be updated at any time owing to a double-buffer
- The LCD controller can operate in Stop mode

3.10 ADC (analog-to-digital converter)

A 12-bit analog-to-digital converters is embedded into STM32L100xx devices with up to 20 external channels, performing conversions in single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADC can be served by the DMA controller.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) can be internally connected to the ADC start trigger and injection trigger, to allow the application to synchronize A/D conversions and timers. An injection mode allows high priority conversions to be done by interrupting a scan mode which runs in as a background task.

The ADC includes a specific low power mode. The converter is able to operate at maximum speed even if the CPU is operating at a very low frequency and has an auto-shutdown function. The ADC's runtime and analog front-end current consumption are thus minimized whatever the MCU operating mode.

3.10.1 Internal voltage reference (V_{REFINT})

The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC and Comparators. V_{REFINT} is internally connected to the ADC_IN17 input channel. It enables accurate monitoring of the V_{DD} value. The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

Table 5. Internal voltage reference measured values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 30 °C $V_{DDA} = 3\text{ V}$	0x1FF8 0078-0x1FF8 0079

3.11 DAC (digital-to-analog converter)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs. The chosen design structure is composed of integrated resistor strings and an amplifier in non-inverting configuration.

This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- left or right data alignment in 12-bit mode
- synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channels' independent or simultaneous conversions
- DMA capability for each channel (including the underrun interrupt)
- external triggers for conversion

Eight DAC trigger inputs are used in the STM32L100xx. The DAC channels are triggered through the timer update outputs that are also connected to different DMA channels.

3.12 Ultralow power comparators and reference voltage

The STM32L100xx embeds two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- one comparator with fixed threshold
- one comparator with rail-to-rail inputs, fast or slow mode. The threshold can be one of the following:
 - DAC output
 - External I/O
 - Internal reference voltage (V_{REFINT}) or V_{REFINT} submultiple (1/4, 1/2, 3/4)

Both comparators can wake up from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low power / low current output buffer (driving current capability of 1 μ A typical).

3.13 Routing interface

This interface controls the internal routing of I/Os to TIM2, TIM3, TIM4 and to the comparator and reference voltage output.

3.14 Timers and watchdogs

The ultralow power STM32L100xx devices include six general-purpose timers, two basic timers and two watchdog timers.

[Table 6](#) compares the features of the general-purpose and basic timers.

Table 6. Timer feature comparison

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2, TIM3, TIM4	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM9	16-bit	Up	Any integer between 1 and 65536	No	2	No
TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No
TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

3.14.1 General-purpose timers (TIM2, TIM3, TIM4, TIM9, TIM10 and TIM11)

There are six synchronizable general-purpose timers embedded in the STM32L100xx devices (see [Table 6](#) for differences).

TIM2, TIM3, TIM4

These timers are based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. They feature 4 independent channels each for input capture/output compare, PWM or one-pulse mode output. This gives up to 12 input captures/output compares/PWMs on the largest packages.

The TIM2, TIM3, TIM4 general-purpose timers can work together or with the TIM10, TIM11 and TIM9 general-purpose timers via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

TIM2, TIM3, TIM4 all have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

TIM10, TIM11 and TIM9

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler. TIM10 and TIM11 feature one independent channel, whereas TIM9 has two independent channels for input capture/output compare, PWM or one-pulse mode output. They can be synchronized with the TIM2, TIM3, TIM4 full-featured general-purpose timers.

They can also be used as simple time bases and be clocked by the LSE clock source (32.768 kHz) to provide time bases independent from the main CPU clock.

3.14.2 Basic timers (TIM6 and TIM7)

These timers are mainly used for DAC trigger generation. They can also be used as generic 16-bit time bases.

3.14.3 SysTick timer

This timer is dedicated to the OS, but could also be used as a standard downcounter. It is based on a 24-bit downcounter with autoreload capability and a programmable clock source. It features a maskable system interrupt generation when the counter reaches 0.

3.14.4 Independent watchdog (IWDG)

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 37 kHz internal RC and, as it operates independently of the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes. The counter can be frozen in debug mode.

3.14.5 Window watchdog (WWDG)

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.15 Communication interfaces

3.15.1 I²C bus

Up to two I²C bus interfaces can operate in multimaster and slave modes. They can support standard and fast modes.

They support dual slave addressing (7-bit only) and both 7- and 10-bit addressing in master mode. A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SM Bus 2.0/PM Bus.

3.15.2 Universal synchronous/asynchronous receiver transmitter (USART)

All USART interfaces are able to communicate at speeds of up to 4 Mbit/s. They provide hardware management of the CTS and RTS signals. They support IrDA SIR ENDEC, are ISO 7816 compliant and have LIN Master/Slave capability.

All USART interfaces can be served by the DMA controller.

3.15.3 Serial peripheral interface (SPI)

Up to two SPIs are able to communicate at up to 16 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

Both SPIs can be served by the DMA controller.

3.15.4 Universal serial bus (USB)

The STM32L100xx embeds a USB device peripheral compatible with the USB full speed 12 Mbit/s. The USB interface implements a full speed (12 Mbit/s) function interface. It has software-configurable endpoint setting and supports suspend/resume. The dedicated 48 MHz clock is generated from the internal main PLL (the clock source must use a HSE crystal oscillator).

3.16 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.17 Development support

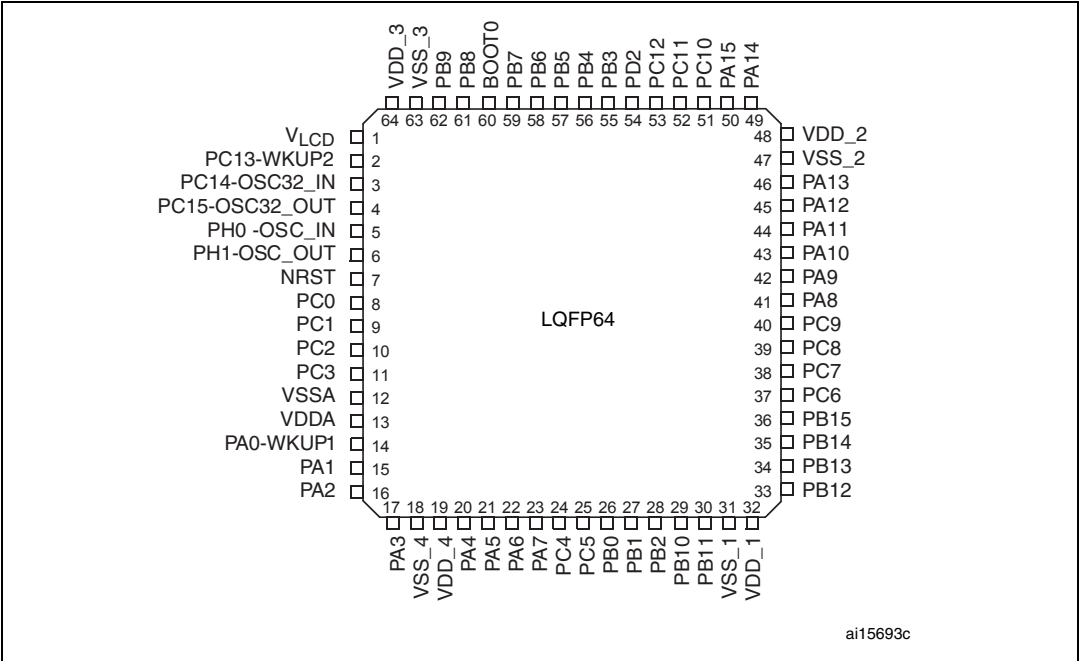
Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG JTMS and JTCK pins are shared with SWDAT and SWCLK, respectively, and a specific sequence on the JTMS pin is used to switch between JTAG-DP and SW-DP.

The JTAG port can be permanently disabled with a JTAG fuse.

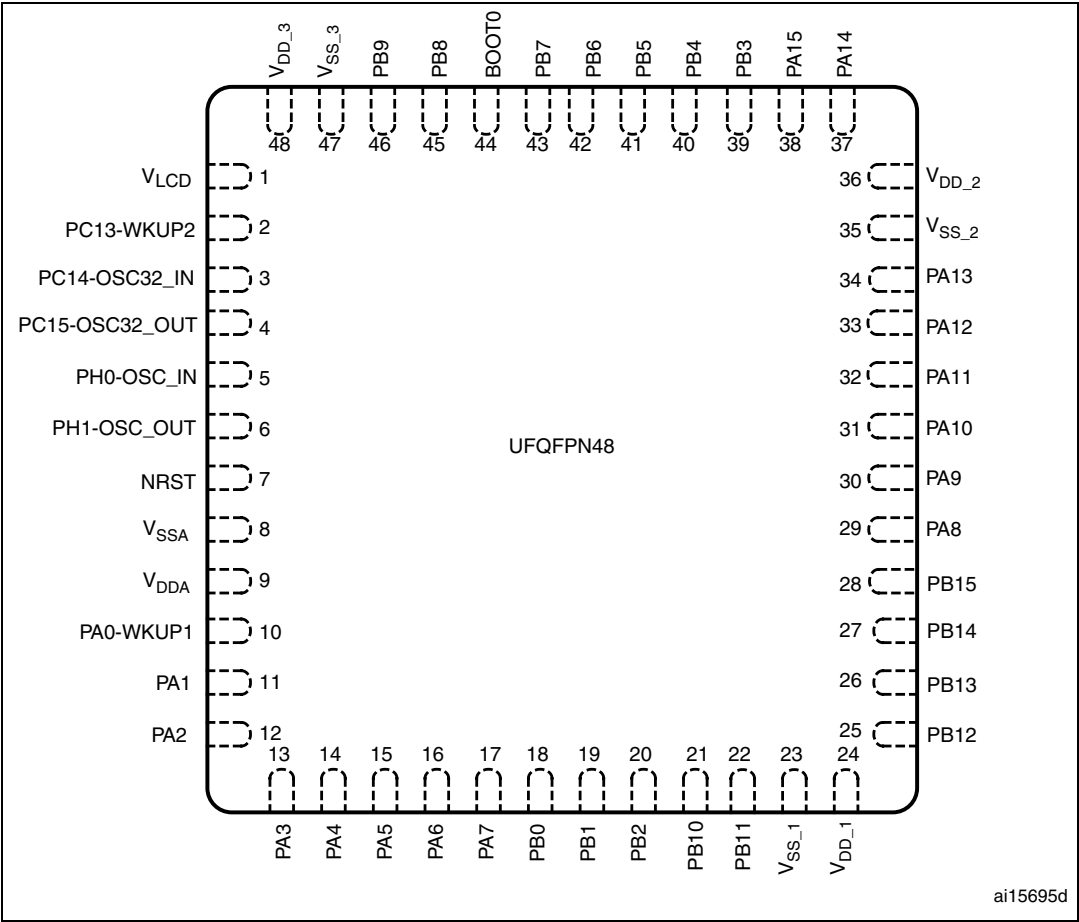
4 Pin descriptions

Figure 3. STM32L100xx LQFP64 pinout



1. This figure shows the package top view.

Figure 4. STM32L100xx UFQFPN48 pinout



1. This figure shows the package top view.

Table 7. STM32L100xx pin definitions

Pins		Pin name	Type ⁽¹⁾	I/O Level ⁽²⁾	Main function ⁽³⁾ (after reset)	Alternate functions
LQFP64	UFQFPN48					
1	1	V _{LCD}	S		V _{LCD}	
2	2	PC13-WKUP2	I/O	FT	PC13	RTC_TAMP1/RTC_TS/RTC_OUT/WKUP2
3	3	PC14- OSC32_IN ⁽⁴⁾	I/O		PC14	OSC32_IN
4	4	PC15- OSC32_OUT ⁽⁵⁾	I/O		PC15	OSC32_OUT
5	5	PH0-OSC_IN ⁽⁵⁾	I		PH0	OSC_IN
6	6	PH1-OSC_OUT	O		PH1	OSC_OUT
7	7	NRST	I/O		NRST	
8	-	PC0	I/O	FT	PC0	ADC_IN10/LCD_SEG18/COMP1_INP
9	-	PC1	I/O	FT	PC1	ADC_IN11/LCD_SEG19/COMP1_INP
10	-	PC2	I/O	FT	PC2	ADC_IN12/LCD_SEG20/COMP1_INP
11	-	PC3	I/O		PC3	ADC_IN13/LCD_SEG21/COMP1_INP
12	8	V _{SSA}	S		V _{SSA}	
13	9	V _{DDA}	S		V _{DDA}	
14	10	PA0-WKUP1	I/O	FT	PA0	WKUP1/USART2_CTS/ADC_IN0/TIM2_CH1_ETR/ COMP1_INP
15	11	PA1	I/O	FT	PA1	USART2_RTS/ADC_IN1/TIM2_CH2/LCD_SEG0/ COMP1_INP
16	12	PA2	I/O	FT	PA2	USART2_TX/ADC_IN2/TIM2_CH3/TIM9_CH1/ LCD_SEG1/COMP1_INP
17	13	PA3	I/O		PA3	USART2_RX/ADC_IN3/TIM2_CH4/TIM9_CH2/ LCD_SEG2/COMP1_INP
18	-	V _{SS_4}	S		V _{SS_4}	
19	-	V _{DD_4}	S		V _{DD_4}	
20	14	PA4	I/O		PA4	SPI1_NSS/USART2_CK/ ADC_IN4/DAC_OUT1/COMP1_INP
21	15	PA5	I/O		PA5	SPI1_SCK/ADC_IN5/ DAC_OUT2/TIM2_CH1_ETR/COMP1_INP
22	16	PA6	I/O	FT	PA6	SPI1_MISO/ADC_IN6/TIM3_CH1/TIM1_BKIN/ LCD_SEG3/TIM10_CH1/COMP1_INP

Table 7. STM32L100xx pin definitions (continued)

Pins		Pin name	Type ⁽¹⁾	I/O Level ⁽²⁾	Main function ⁽³⁾ (after reset)	Alternate functions
LQFP64	UFQFPN48					
23	17	PA7	I/O	FT	PA7	SPI1_MOSI/ADC_IN7/TIM3_CH2/TIM1_CH1N/ LCD_SEG4/TIM11_CH1/COMP1_INP
24	-	PC4	I/O	FT	PC4	ADC_IN14/LCD_SEG22/COMP1_INP
25	-	PC5	I/O	FT	PC5	ADC_IN15/LCD_SEG23/COMP1_INP
26	18	PB0	I/O		PB0	ADC_IN8/TIM3_CH3/LCD_SEG5/ COMP1_INP/VREF_OUT
27	19	PB1	I/O	FT	PB1	ADC_IN9/TIM3_CH4/LCD_SEG6/ COMP1_INP/VREF_OUT
28	20	PB2	I/O	FT	PB2/BOOT1	
29	21	PB10	I/O	FT	PB10	I2C2_SCL/USART3_TX/TIM2_CH3/LCD_SEG10
30	22	PB11	I/O	FT	PB11	I2C2_SDA/USART3_RX/TIM2_CH4/LCD_SEG11
31	23	V _{SS_1}	S		V _{SS_1}	
32	24	V _{DD_1}	S		V _{DD_1}	
33	25	PB12	I/O	FT	PB12	SPI2_NSS/I2C2_SMBA/USART3_CK/LCD_SEG12/ ADC_IN18/COMP1_INP/TIM10_CH1
34	26	PB13	I/O	FT	PB13	SPI2_SCK/USART3_CTS/LCD_SEG13/ADC_IN19/ COMP1_INP/TIM9_CH1
35	27	PB14	I/O	FT	PB14	SPI2_MISO/USART3_RTS/LCD_SEG14/ADC_IN20/ COMP1_INP/TIM9_CH2
36	28	PB15	I/O	FT	PB15	SPI2_MOSI/TIM1_CH3N/LCD_SEG15/ADC_IN21/ COMP1_INP/TIM11_CH1/RTC_REFIN
37	-	PC6	I/O	FT	PC6	TIM3_CH1/LCD_SEG24
38	-	PC7	I/O	FT	PC7	TIM3_CH2/LCD_SEG25
39	-	PC8	I/O	FT	PC8	TIM3_CH3/LCD_SEG26
40	-	PC9	I/O	FT	PC9	TIM3_CH4/LCD_SEG27
41	29	PA8	I/O	FT	PA8	USART1_CK/MCO/LCD_COM0
42	30	PA9	I/O	FT	PA9	USART1_TX/LCD_COM1
43	31	PA10	I/O	FT	PA10	USART1_RX/LCD_COM2
44	32	PA11	I/O	FT	PA11	USART1_CTS/USB_DM/SPI1_MISO
45	33	PA12	I/O	FT	PA12	USART1_RTS/USB_DP/SPI1_MOSI

Table 7. STM32L100xx pin definitions (continued)

Pins		Pin name	Type ⁽¹⁾	I/O Level ⁽²⁾	Main function ⁽³⁾ (after reset)	Alternate functions
LQFP64	UFQFPN48					
46	34	PA13	I/O	FT	JTMS/ SWDAT	
47	35	V _{SS_2}	S		V _{SS_2}	
48	36	V _{DD_2}	S		V _{DD_2}	
49	37	PA14	I/O	FT	JTCK /SWCLK	
50	38	PA15	I/O	FT	JTDI	TIM2_CH1_ETR/PA15/SPI1_NSS/LCD_SEG17
51	-	PC10	I/O	FT	PC10	USART3_TX/LCD_SEG28/LCD_SEG40/ LCD_COM4
52	-	PC11	I/O	FT	PC11	USART3_RX/LCD_SEG29/LCD_SEG41/ LCD_COM5
53	-	PC12	I/O	FT	PC12	USART3_CK/LCD_SEG30/LCD_SEG42/ LCD_COM6
54	-	PD2	I/O	FT	PD2	TIM3_ETR/LCD_SEG43/LCD_COM7
55	39	PB3	I/O	FT	JTDO	TIM2_CH2/PB3/SPI1_SCK/COMP2_INM/ LCD_SEG7
56	40	PB4	I/O	FT	NJTRST	TIM3_CH1/PB4/ SPI1_MISO/COMP2_INP/LCD_SEG8
57	41	PB5	I/O	FT	PB5	I2C1_SMBA/TIM3_CH2/SPI1_MOSI/COMP2_INP/ LCD_SEG9
58	42	PB6	I/O	FT	PB6	I2C1_SCL/TIM4_CH1/USART1_TX
59	43	PB7	I/O	FT	PB7	I2C1_SDA/TIM4_CH2/ USART1_RX/PVD_IN
60	44	BOOT0	I		BOOT0	
61	45	PB8	I/O	FT	PB8	TIM4_CH3/I2C1_SCL/LCD_SEG16/TIM10_CH1
62	46	PB9	I/O	FT	PB9	TIM4_CH4/I2C1_SDA/LCD_COM3/TIM11_CH1
63	47	V _{SS_3}	S		V _{SS_3}	
64	48	V _{DD_3}	S		V _{DD_3}	

1. I = input, O = output, S = supply.

2. FT = 5 V tolerant.

3. Function availability depends on the chosen device. For devices having reduced peripheral counts, it is always the lower number of peripheral that is included. For example, if a device has only one SPI and two USARTs, they will be called SPI1 and USART1 & USART2, respectively. Refer to [Table 1 on page 10](#).

4. The PC14 and PC15 I/Os are only configured as OSC32_IN/OSC32_OUT when the LSE oscillator is on (by setting the LSEON bit in the RCC_CSR register). The LSE oscillator pins OSC32_IN/OSC32_OUT can be used as general-purpose PC14/PC15 I/Os, respectively, when the LSE oscillator is off (after reset, the LSE oscillator is off). The LSE has priority over the GPIO function. For more details, refer to Using the OSC32_IN/OSC32_OUT pins as GPIO PC14/PC15 port pins section in the STM32Lxx reference manual (RM0038).
5. The PH0 and PH1 I/Os are only configured as OSC_IN/OSC_OUT when the HSE oscillator is on (by setting the HSEON bit in the RCC_CR register). The HSE oscillator pins OSC_IN/OSC_OUT can be used as general-purpose PH0/PH1 I/Os, respectively, when the HSE oscillator is off (after reset, the HSE oscillator is off). The HSE has priority over the GPIO function.



Table 8. Alternate function input/output

Port name	Digital alternate function number															
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFOI6	AFIO7	AFIO8	AFIO9	AFIO10	AFIO11	AFIO12	AFIO13	AFIO14	AFIO15
	Alternate function															
	SYSTEM	TIM2	TIM3/4	TIM9/10/11	I2C1/2	SPI1/2	N/A	USART 1/2/3	N/A	N/A	USB	LCD	N/A	N/A	RI	SYSTEM
BOOT0	BOOT0															
NRST	NRST															
PA0-WKUP1	WKUP1	TIM2_CH1_ETR						USART2_CTS							TIMx_IC1	EVENTOUT
PA1		TIM2_CH2						USART2_RTS				[SEG0]			TIMx_IC2	EVENTOUT
PA2		TIM2_CH3		TIM9_CH1				USART2_TX				[SEG1]			TIMx_IC3	EVENTOUT
PA3		TIM2_CH4		TIM9_CH2				USART2_RX				[SEG2]			TIMx_IC4	EVENTOUT
PA4						SPI1_NSS		USART2_CK							TIMx_IC1	EVENTOUT
PA5		TIM2_CH1_ETR				SPI1_SCK									TIMx_IC2	EVENTOUT
PA6			TIM3_CH1	TIM10_CH1		SPI1_MISO						[SEG3]			TIMx_IC3	EVENTOUT
PA7			TIM3_CH2	TIM11_CH1		SPI1_MOSI						[SEG4]			TIMx_IC4	EVENTOUT
PA8	MCO							USART1_CK				[COM0]			TIMx_IC1	EVENTOUT
PA9								USART1_TX				[COM1]			TIMx_IC2	EVENTOUT
PA10								USART1_RX				[COM2]			TIMx_IC3	EVENTOUT
PA11						SPI1_MISO		USART1_CTS			DM				TIMx_IC4	EVENTOUT
PA12						SPI1_MOSI		USART1_RTS			DP				TIMx_IC1	EVENTOUT
PA13	JTMS-SWDAT														TIMx_IC2	EVENTOUT
PA14	JTCK-SWCLK														TIMx_IC3	EVENTOUT



Table 8. Alternate function input/output (continued)

Port name	Digital alternate function number															
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFOI6	AFIO7	AFIO8	AFIO9	AFIO10	AFIO11	AFIO12	AFIO13	AFIO14	AFIO15
	Alternate function															
	SYSTEM	TIM2	TIM3/4	TIM9/10/11	I2C1/2	SPI1/2	N/A	USART 1/2/3	N/A	N/A	USB	LCD	N/A	N/A	RI	SYSTEM
PA15	JTDI	TIM2_CH1_ETR				SPI1_NSS						SEG17			TIMx_IC4	EVENTOUT
PB0			TIM3_CH3									[SEG5]				EVENTOUT
PB1			TIM3_CH4									[SEG6]				EVENTOUT
PB2	BOOT1															EVENTOUT
PB3	JTDO	TIM2_CH2				SPI1_SCK						[SEG7]				EVENTOUT
PB4	JTRST		TIM3_CH1			SPI1_MISO						[SEG8]				EVENTOUT
PB5			TIM3_CH2		I2C1_SMBA	SPI1_MOSI						[SEG9]				EVENTOUT
PB6			TIM4_CH1		I2C1_SCL			USART1_TX								EVENTOUT
PB7			TIM4_CH2		I2C1_SDA			USART1_RX								EVENTOUT
PB8			TIM4_CH3	TIM10_CH1*	I2C1_SCL							SEG16				EVENTOUT
PB9			TIM4_CH4	TIM11_CH1*	I2C1_SDA							[COM3]				EVENTOUT
PB10		TIM2_CH3			I2C2_SCL			USART3_TX				SEG10				EVENTOUT
PB11		TIM2_CH4			I2C2_SDA			USART3_RX				SEG11				EVENTOUT
PB12				TIM10_CH1	I2C2_SMBA	SPI2_NSS		USART3_CK				SEG12				EVENTOUT
PB13				TIM9_CH1		SPI2_SCK		USART3_CTS				SEG13				EVENTOUT
PB14				TIM9_CH2		SPI2_MISO		USART3_RTS				SEG14				EVENTOUT
PB15	RTC_REFIN			TIM11_CH1		SPI2_MOSI						SEG15				EVENTOUT
PC0												SEG18			TIMx_IC1	EVENTOUT
PC1												SEG19			TIMx_IC2	EVENTOUT



Table 8. Alternate function input/output (continued)

Port name	Digital alternate function number															
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFOI6	AFIO7	AFIO8	AFIO9	AFIO10	AFIO11	AFIO12	AFIO13	AFIO14	AFIO15
	Alternate function															
	SYSTEM	TIM2	TIM3/4	TIM9/10/11	I2C1/2	SPI1/2	N/A	USART 1/2/3	N/A	N/A	USB	LCD	N/A	N/A	RI	SYSTEM
PC2												SEG20			TIMx_IC3	EVENTOUT
PC3												SEG21			TIMx_IC4	EVENTOUT
PC4												SEG22			TIMx_IC1	EVENTOUT
PC5												SEG23			TIMx_IC2	EVENTOUT
PC6			TIM3_CH1									SEG24			TIMx_IC3	EVENTOUT
PC7			TIM3_CH2									SEG25			TIMx_IC4	EVENTOUT
PC8			TIM3_CH3									SEG26			TIMx_IC1	EVENTOUT
PC9			TIM3_CH4									SEG27			TIMx_IC2	EVENTOUT
PC10								USART3_TX				COM4 / SEG28 / SEG40			TIMx_IC3	EVENTOUT
PC11								USART3_RX				COM5 / SEG29 / SEG41			TIMx_IC4	EVENTOUT
PC12								USART3_CK				COM6 / SEG30 / SEG42			TIMx_IC1	EVENTOUT
PC13- WKUP2	RTC_TAMP1/ RTC_TS/ RTC_OUT/ WKUP2														TIMx_IC2	EVENTOUT
PC14- OSC32_IN	OSC32_IN														TIMx_IC3	EVENTOUT
PC15- OSC32_OUT	OSC32_OUT														TIMx_IC4	EVENTOUT
PD2			TIM3_ETR									COM7 / SEG31 / SEG43			TIMx_IC3	EVENTOUT

Table 8. Alternate function input/output (continued)

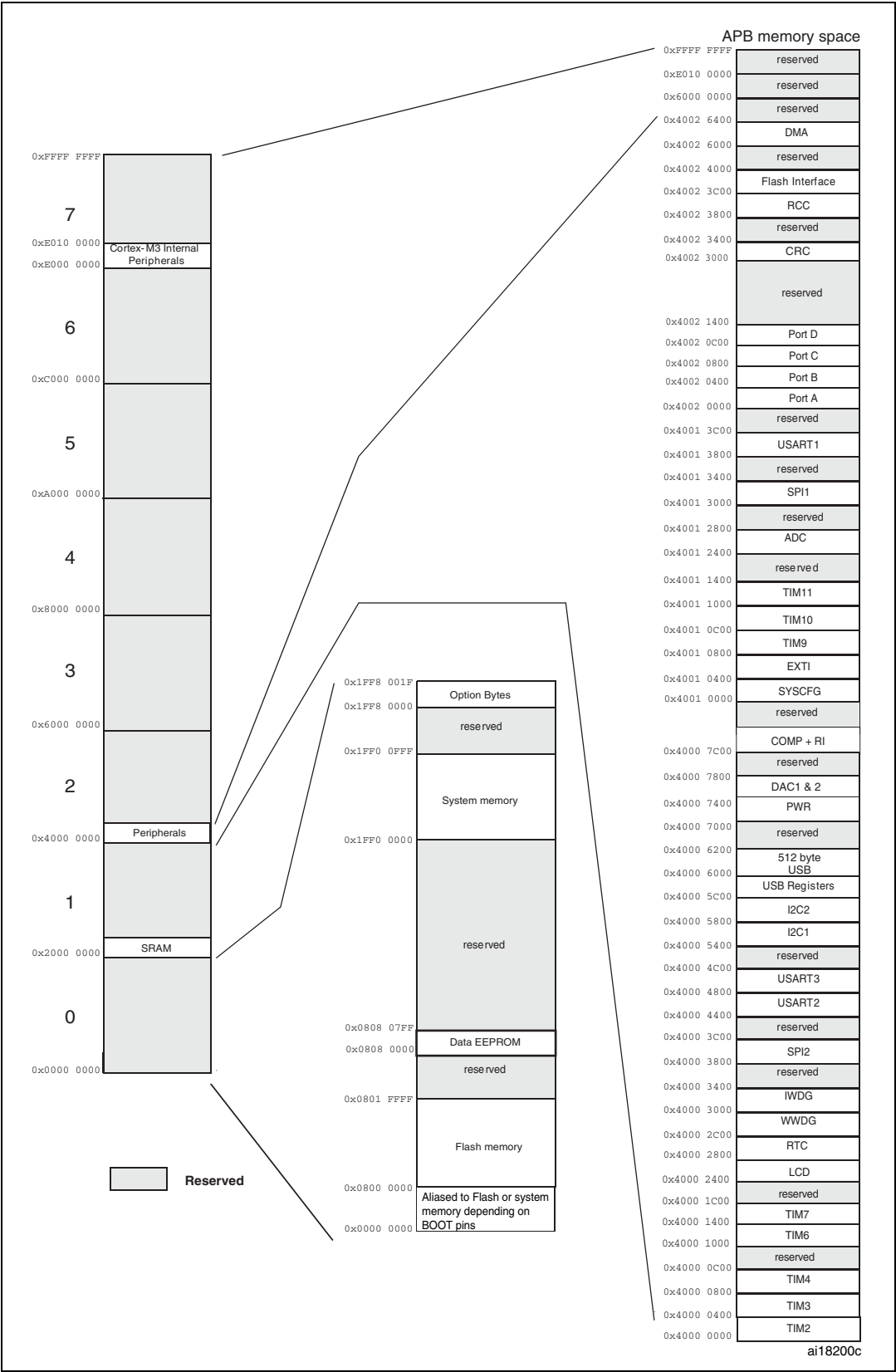
Port name	Digital alternate function number															
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFOI6	AFIO7	AFIO8	AFIO9	AFIO10	AFIO11	AFIO12	AFIO13	AFIO14	AFIO15
	Alternate function															
	SYSTEM	TIM2	TIM3/4	TIM9/10/11	I2C1/2	SPI1/2	N/A	USART 1/2/3	N/A	N/A	USB	LCD	N/A	N/A	RI	SYSTEM
PH0-OSC_IN	OSC_IN															
PH1-OSC_OUT	OSC_OUT															



5 Memory mapping

The memory map is shown in the following figure.

Figure 5. Memory map



6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS} .

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25\text{ }^{\circ}\text{C}$ and $T_A = T_{A\text{max}}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation ($\text{mean} \pm 3\Sigma$).

6.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25\text{ }^{\circ}\text{C}$, $V_{DD} = 3.6\text{ V}$ (for the $1.8\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated ($\text{mean} \pm 2\Sigma$).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in [Figure 6](#).

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 7](#).

Figure 6. Pin loading conditions

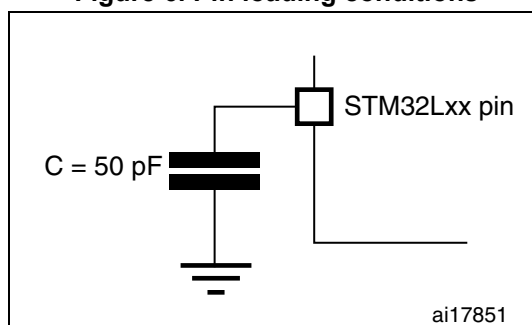
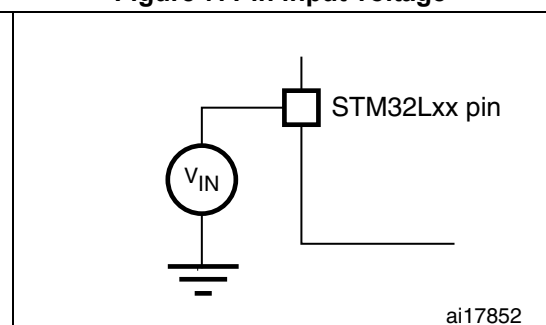
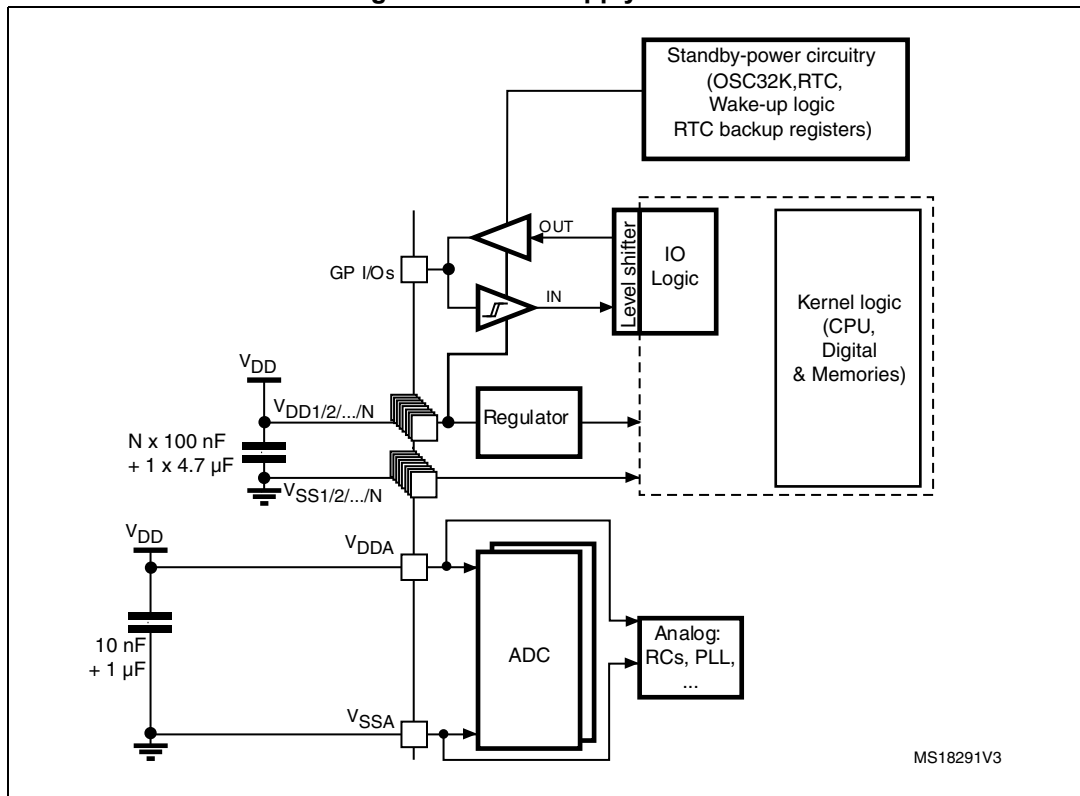


Figure 7. Pin input voltage



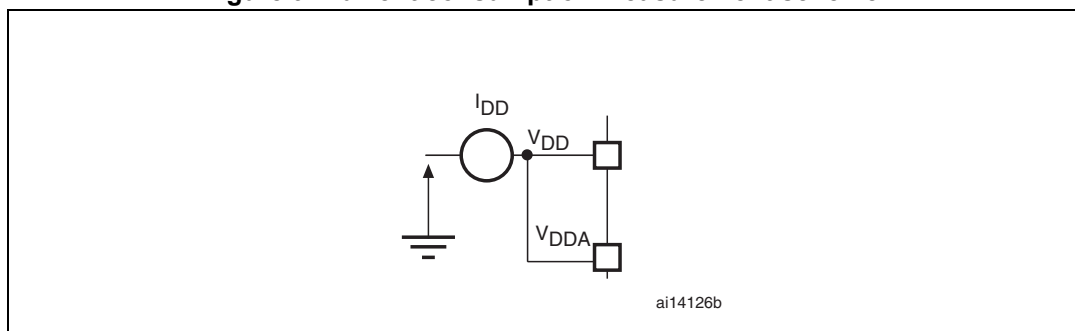
6.1.6 Power supply scheme

Figure 8. Power supply scheme



6.1.7 Current consumption measurement

Figure 9. Current consumption measurement scheme



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in [Table 9: Voltage characteristics](#), [Table 10: Current characteristics](#), and [Table 11: Thermal characteristics](#) may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 9. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
$V_{DD}-V_{SS}$	External main supply voltage (including V_{DDA} and V_{DD}) ⁽¹⁾	-0.3	4.0	V
$V_{IN}^{(2)}$	Input voltage on five-volt tolerant pin	$V_{SS}-0.3$	$V_{DD}+4.0$	
	Input voltage on any other pin	$V_{SS}-0.3$	4.0	
$ \Delta V_{DDx} $	Variations between different V_{DD} power pins		50	mV
$ V_{SSx}-V_{SS} $	Variations between all different ground pins		50	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see Section 6.3.10		

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to [Table 10](#) for maximum allowed injected current values.

Table 10. Current characteristics

Symbol	Ratings	Max.	Unit
I_{VDD}	Total current into V_{DD}/V_{DDA} power lines (source) ⁽¹⁾	80	mA
I_{VSS}	Total current out of V_{SS} ground lines (sink) ⁽¹⁾	80	
I_{IO}	Output current sunk by any I/O and control pin	25	
	Output current sourced by any I/O and control pin	- 25	
$I_{INJ(PIN)}^{(2)}$	Injected current on five-volt tolerant I/O ⁽³⁾	+0 /-5	
	Injected current on any other pin ⁽⁴⁾	± 5	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins) ⁽⁵⁾	± 25	

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. Negative injection disturbs the analog performance of the device. See note in [Section 6.3.16](#).
3. Positive current injection is not possible on these I/Os. A negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to [Table 9](#) for maximum allowed input voltage values.
4. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to [Table 9: Voltage characteristics](#) for the maximum allowed input voltage values.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 11. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	105	°C

6.3 Operating conditions

6.3.1 General operating conditions

Table 12. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency		0	32	MHz
f_{PCLK1}	Internal APB1 clock frequency		0	32	
f_{PCLK2}	Internal APB2 clock frequency		0	32	
V_{DD}	Standard operating voltage	BOR detector enabled, (at power-on)	1.8	3.6	V
		BOR detector disabled, after power on	1.65	3.6	
$V_{DDA}^{(1)}$	Analog operating voltage	Must be the same voltage as $V_{DD}^{(2)}$	1.8	3.6	V
P_D	Power dissipation at $T_A = 85\text{ °C}^{(3)}$	LQFP64 package		444	mW
T_A	Temperature range	Maximum power dissipation	–40	85	°C
T_J	Junction temperature range	$-40\text{ °C} \leq T_A \leq 85\text{ °C}$	–40	105	°C

1. When the ADC is used, refer to [Table 52: ADC characteristics](#).
2. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and operation.
3. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_J max (see [Table 61: Thermal characteristics on page 98](#)).

6.3.2 Embedded reset and power control block characteristics

The parameters given in the following table are derived from the tests performed under the ambient temperature condition summarized in the following table.

Table 13. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{VDD}^{(1)}$	V_{DD} rise time rate	BOR detector enabled	0		∞	$\mu s/V$
	V_{DD} fall time rate	BOR detector enabled	20		∞	
		BOR detector disabled	0		1000	
$T_{RSTTEMPO}^{(1)}$	Reset temporization	V_{DD} rising, BOR enabled		2	3.3	ms
$V_{POR/PDR}$	Power on/power down reset threshold	Falling edge	1	1.5	1.65	V
		Rising edge	1.3	1.5	1.65	
V_{BOR0}	Brown-out reset threshold 0	Falling edge	1.67	1.7	1.74	V
		Rising edge	1.69	1.76	1.8	
V_{BOR1}	Brown-out reset threshold 1	Falling edge	1.87	1.93	1.97	
		Rising edge	1.96	2.03	2.07	
V_{BOR2}	Brown-out reset threshold 2	Falling edge	2.22	2.30	2.35	
		Rising edge	2.31	2.41	2.44	
V_{BOR3}	Brown-out reset threshold 3	Falling edge	2.45	2.55	2.60	
		Rising edge	2.54	2.66	2.7	
V_{BOR4}	Brown-out reset threshold 4	Falling edge	2.68	2.8	2.85	
		Rising edge	2.78	2.9	2.95	
V_{PVD0}	Programmable voltage detector threshold 0	Falling edge	1.8	1.85	1.88	
		Rising edge	1.88	1.94	1.99	
V_{PVD1}	PVD threshold 1	Falling edge	1.98	2.04	2.09	
		Rising edge	2.08	2.14	2.18	
V_{PVD2}	PVD threshold 2	Falling edge	2.20	2.24	2.28	
		Rising edge	2.28	2.34	2.38	
V_{PVD3}	PVD threshold 3	Falling edge	2.39	2.44	2.48	
		Rising edge	2.47	2.54	2.58	
V_{PVD4}	PVD threshold 4	Falling edge	2.57	2.64	2.69	
		Rising edge	2.68	2.74	2.79	
V_{PVD5}	PVD threshold 5	Falling edge	2.77	2.83	2.88	
		Rising edge	2.87	2.94	2.99	
V_{PVD6}	PVD threshold 6	Falling edge	2.97	3.05	3.09	
		Rising edge	3.08	3.15	3.20	

Table 13. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{hyst}	Hysteresis voltage	BOR0 threshold		40		mV
		All BOR and PVD thresholds excepting BOR0		100		

1. Guaranteed by characterization, not tested in production.

6.3.3 Embedded internal reference voltage

The parameters given in the following table are based on characterization results, unless otherwise specified.

Table 14. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{\text{REFINT out}}^{(1)}$	Internal reference voltage	$-40\text{ }^{\circ}\text{C} < T_J < +105\text{ }^{\circ}\text{C}$	1.202	1.224	1.242	V
I_{REFINT}	Internal reference current consumption			1.4	2.3	μA
T_{VREFINT}	Internal reference startup time			2	3	ms
$V_{\text{VREF_MEAS}}$	V_{DDA} voltage during V_{REFINT} factory measure		2.99	3	3.01	V
$A_{\text{VREF_MEAS}}$	Accuracy of factory-measured V_{REF} value ⁽²⁾	Including uncertainties due to ADC and V_{DDA} values			± 5	mV
$T_{\text{Coeff}}^{(3)}$	Temperature coefficient	$-40\text{ }^{\circ}\text{C} < T_J < +105\text{ }^{\circ}\text{C}$		20	50	ppm/ $^{\circ}\text{C}$
		$0\text{ }^{\circ}\text{C} < T_J < +50\text{ }^{\circ}\text{C}$			20	
$A_{\text{Coeff}}^{(3)}$	Long-term stability	1000 hours, $T = 25\text{ }^{\circ}\text{C}$			1000	ppm
$\text{VDDCoeff}^{(3)}$	Voltage coefficient	$3.0\text{ V} < V_{\text{DDA}} < 3.6\text{ V}$			2000	ppm/V
$T_{\text{S_vrefint}}^{(3)(4)}$	ADC sampling time when reading the internal reference voltage			5	10	μs
$T_{\text{ADC_BUF}}^{(3)}$	Startup time of reference voltage buffer for ADC				10	μs
$I_{\text{BUF_ADC}}^{(3)}$	Consumption of reference voltage buffer for ADC			13.5	25	μA
$I_{\text{VREF_OUT}}^{(3)}$	VREF_OUT output current ⁽⁵⁾				1	μA
$C_{\text{VREF_OUT}}^{(3)}$	VREF_OUT output load				50	pF
$I_{\text{LPBUF}}^{(3)}$	Consumption of reference voltage buffer for VREF_OUT and COMP			730	1200	nA
$V_{\text{REFINT_DIV1}}^{(3)}$	1/4 reference voltage		24	25	26	% V_{REFINT}
$V_{\text{REFINT_DIV2}}^{(3)}$	1/2 reference voltage		49	50	51	
$V_{\text{REFINT_DIV3}}^{(3)}$	3/4 reference voltage		74	75	76	

1. Tested in production.
2. The internal V_{REF} value is individually measured in production and stored in dedicated EEPROM bytes.
3. Guaranteed by design, not tested in production.
4. Shortest sampling time can be determined in the application by multiple iterations.
5. To guarantee less than 1% V_{REF_OUT} deviation.

6.3.4 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code. The current consumption is measured as described in [Figure 9: Current consumption measurement scheme](#).

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code.

Maximum current consumption

The MCU is placed under the following conditions:

- $V_{DD} = 3.6\text{ V}$
- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted depending on f_{HCLK} frequency and voltage range
- Prefetch and 64-bit access are enabled in configurations with 1 wait state

The parameters given in [Table 15](#), [Table 12](#) and [Table 13](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 12](#).

Table 15. Current consumption in Run mode, code with data processing running from Flash

Symbol	Parameter	Conditions		f _{HCLK}	Typ	Max ⁽¹⁾		Unit
						55 °C	85 °C	
I _{DD} (Run from Flash)	Supply current in Run mode, code executed from Flash	f _{HSE} = f _{HCLK} up to 8 MHz, included f _{HSE} = f _{HCLK} /2 above 8 MHz (PLL ON) ⁽²⁾	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	1 MHz	270	400	400	μA
				2 MHz	470	600	600	
				4 MHz	890	1025	1025	
			Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	4 MHz	1	1.3	1.3	mA
				8 MHz	2	2.5	2.5	
				16 MHz	3.9	5	5	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	8 MHz	2.16	3	3	
				16 MHz	4.8	5.5	5.5	
				32 MHz	9.6	11	11	
		HSI clock source (16 MHz)	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	4	5	5	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	9.4	11	11	
		MSI clock, 65 kHz	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	65 kHz	0.05	0.085	0.09	
		MSI clock, 524 kHz		524 kHz	0.15	0.185	0.19	
		MSI clock, 4.2 MHz		4.2 MHz	0.9	1	1	

1. Based on characterization, not tested in production, unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 16. Current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conditions		f _{HCLK}	Typ	Max ⁽¹⁾		Unit
						55 °C	85 °C	
I _{DD} (Run from RAM)	Supply current in Run mode, code executed from RAM, Flash switched off	f _{HSE} = f _{HCLK} up to 8 MHz, included f _{HSE} = f _{HCLK} /2 above 8 MHz (PLL ON) ⁽²⁾	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	1 MHz	200	300	300	μA
				2 MHz	380	500	500	
				4 MHz	720	860	860	
			Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	4 MHz	0.9	1	1	mA
				8 MHz	1.65	2	2	
				16 MHz	3.2	3.7	3.7	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	8 MHz	2	2.5	2.5	
				16 MHz	4	4.5	4.5	
				32 MHz	7.7	8.5	8.5	
		HSI clock source (16 MHz)	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	3.3	3.8	3.8	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	7.8	9.2	9.2	
		MSI clock, 65 kHz	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	65 kHz	40	60	60	μA
		MSI clock, 524 kHz		524 kHz	110	140	140	
		MSI clock, 4.2 MHz		4.2 MHz	700	800	800	

1. Based on characterization, not tested in production, unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 17. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f _{HCLK}	Typ	Max ⁽¹⁾		Unit
						55 °C	85 °C	
I _{DD} (Sleep)	Supply current in Sleep mode, code executed from RAM, Flash switched OFF	f _{HSE} = f _{HCLK} up to 16 MHz included, f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	1 MHz	80	140	140	μA
				2 MHz	150	210	210	
				4 MHz	280	330	330	
			Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	4 MHz	280	400	400	
				8 MHz	450	550	550	
				16 MHz	900	1050	1050	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	8 MHz	550	650	650	
				16 MHz	1050	1200	1200	
				32 MHz	2300	2500	2500	
		HSI clock source (16 MHz)	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	1000	1100	1100	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	2300	2500	2500	
		MSI clock, 65 kHz		65 kHz	30	50	50	
		MSI clock, 524 kHz	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	524 kHz	50	70	70	
		MSI clock, 4.2 MHz		4.2 MHz	200	240	240	
	Supply current in Sleep mode, code executed from Flash	f _{HSE} = f _{HCLK} up to 16 MHz included, f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	1 MHz	80	140	140	μA
				2 MHz	150	210	210	
				4 MHz	290	350	350	
			Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	4 MHz	300	400	400	
				8 MHz	500	600	600	
				16 MHz	1000	1100	1100	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	8 MHz	550	650	650	
				16 MHz	1050	1200	1200	
				32 MHz	2300	2500	2500	
		HSI clock source (16 MHz)	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	1000	1100	1100	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	2300	2500	2500	
I _{DD} (Sleep)	Supply current in Sleep mode, code executed from Flash	MSI clock, 65 kHz	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	65 kHz	40	70	70	μA
		MSI clock, 524 kHz		524 kHz	60	90	90	
		MSI clock, 4.2 MHz		4.2 MHz	210	250	250	

1. Based on characterization, not tested in production, unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register)

Table 18. Current consumption in Low power run mode

Symbol	Parameter	Conditions			Typ	Max (1)	Unit
I_{DD} (LP Run)	Supply current in Low power run mode	All peripherals OFF, code executed from RAM, Flash switched OFF, V_{DD} from 1.8 V to 3.6 V	MSI clock, 65 kHz $f_{HCLK} = 32$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	9	12	μA
				$T_A = 85\text{ }^{\circ}\text{C}$	17.5	24	
			MSI clock, 65 kHz $f_{HCLK} = 65$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	14	17	
				$T_A = 85\text{ }^{\circ}\text{C}$	22	29	
			MSI clock, 131 kHz $f_{HCLK} = 131$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	37	42	
				$T_A = 55\text{ }^{\circ}\text{C}$	37	42	
				$T_A = 85\text{ }^{\circ}\text{C}$	37	42	
		All peripherals OFF, code executed from Flash, V_{DD} from 1.8 V to 3.6 V	MSI clock, 65 kHz $f_{HCLK} = 32$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	24	32	
				$T_A = 85\text{ }^{\circ}\text{C}$	33	42	
			MSI clock, 65 kHz $f_{HCLK} = 65$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	31	40	
				$T_A = 85\text{ }^{\circ}\text{C}$	40	48	
			MSI clock, 131 kHz $f_{HCLK} = 131$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	48	58	
				$T_A = 55\text{ }^{\circ}\text{C}$	54	63	
				$T_A = 85\text{ }^{\circ}\text{C}$	56	65	
I_{DD} Max (LP Run) ⁽²⁾	Max allowed current in Low power run mode	V_{DD} from 1.8 V to 3.6 V				200	

1. Based on characterization, not tested in production, unless otherwise specified.
2. This limitation is related to the consumption of the CPU core and the peripherals that are powered by the regulator. Consumption of the I/Os is not included in this limitation.

Table 19. Current consumption in Low power sleep mode

Symbol	Parameter	Conditions			Typ	Max (1)	Unit
I_{DD} (LP Sleep)	Supply current in Low power sleep mode	All peripherals OFF, V_{DD} from 1.8 V to 3.6 V	MSI clock, 65 kHz $f_{HCLK} = 32$ kHz Flash OFF	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	4.4		μA
			MSI clock, 65 kHz $f_{HCLK} = 32$ kHz Flash ON	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	17.5	25	
				$T_A = 85\text{ }^{\circ}\text{C}$	22	27	
			MSI clock, 65 kHz $f_{HCLK} = 65$ kHz, Flash ON	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	18	26	
				$T_A = 85\text{ }^{\circ}\text{C}$	23	28	
			MSI clock, 131 kHz $f_{HCLK} = 131$ kHz, Flash ON	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	22	30	
				$T_A = 55\text{ }^{\circ}\text{C}$	24	32	
				$T_A = 85\text{ }^{\circ}\text{C}$	26	34	
		TIM9 and USART1 enabled, Flash ON, V_{DD} from 1.8 V to 3.6 V	MSI clock, 65 kHz $f_{HCLK} = 32$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	17.5	25	
				$T_A = 85\text{ }^{\circ}\text{C}$	22	27	
			MSI clock, 65 kHz $f_{HCLK} = 65$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	18	26	
				$T_A = 85\text{ }^{\circ}\text{C}$	23	28	
			MSI clock, 131 kHz $f_{HCLK} = 131$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	22	30	
				$T_A = 55\text{ }^{\circ}\text{C}$	24	32	
				$T_A = 85\text{ }^{\circ}\text{C}$	26	34	
I_{DD} Max (LP Sleep)	Max allowed current in Low power Sleep mode	V_{DD} from 1.8 V to 3.6 V				200	

1. Based on characterization, not tested in production, unless otherwise specified.

Table 20. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions			Typ ⁽¹⁾	Max (1)(2)	Unit
I _{DD} (Stop with RTC)	Supply current in Stop mode with RTC enabled	RTC clocked by LSI, regulator in LP mode, HSI and HSE OFF (no independent watchdog)	LCD OFF	T _A = -40°C to 25°C V _{DD} = 1.8 V	1.2	2.75	μA
				T _A = -40°C to 25°C	1.4	4	
				T _A = 55°C	2.6	6	
				T _A = 85°C	4.8	10	
			LCD ON (static duty) ⁽³⁾	T _A = -40°C to 25°C	3.3	6	
				T _A = 55°C	4.5	8	
				T _A = 85°C	6.6	12	
			LCD ON (1/8 duty) ⁽⁴⁾	T _A = -40°C to 25°C	7.7	10	
				T _A = 55°C	8.6	12	
				T _A = 85°C	10.7	16	
		RTC clocked by LSE external clock (32.768 kHz), regulator in LP mode, HSI and HSE OFF (no independent watchdog)	LCD OFF	T _A = -40°C to 25°C	1.6	4	
				T _A = 55°C	2.7	6	
				T _A = 85°C	4.8	10	
			LCD ON (static duty) ⁽³⁾	T _A = -40°C to 25°C	3.6	6	
				T _A = 55°C	4.6	8	
				T _A = 85°C	6.7	12	
			LCD ON (1/8 duty) ⁽⁴⁾	T _A = -40°C to 25°C	7.6	10	
				T _A = 55°C	8.6	12	
				T _A = 85°C	10.7	16	
			RTC clocked by LSE (no independent watchdog) ⁽⁵⁾	LCD OFF	T _A = -40°C to 25°C V _{DD} = 1.8 V	1.45	
		T _A = -40°C to 25°C V _{DD} = 3.0 V			1.9		
		T _A = -40°C to 25°C V _{DD} = 3.6 V			2.2		
I _{DD} (Stop)	Supply current in Stop mode (RTC disabled)	Regulator in LP mode, HSI and HSE OFF, independent watchdog and LSI enabled		T _A = -40°C to 25°C	1.1	2.2	μA
		Regulator in LP mode, LSI, HSI and HSE OFF (no independent watchdog)		T _A = -40°C to 25°C	0.5	0.9	
				T _A = 55°C	1.9	5	
						T _A = 85°C	
I _{DD} (WU from Stop)	RMS (root mean square) supply current during wakeup time when exiting from Stop mode	MSI = 4.2 MHz		V _{DD} = 3.0 V T _A = -40°C to 25°C	2		mA
		MSI = 1.05 MHz			1.45		
		MSI = 65 kHz ⁽⁶⁾			1.45		

1. The typical values are given for $V_{DD} = 3.0$ V and max values are given for $V_{DD} = 3.6$ V, unless otherwise specified.
2. Based on characterization, not tested in production, unless otherwise specified
3. LCD enabled with external VLCD, static duty, division ratio = 256, all pixels active, no LCD connected
4. LCD enabled with external VLCD, 1/8 duty, 1/3 bias, division ratio = 64, all pixels active, no LCD connected.
5. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8pF loading capacitors.
6. When MSI = 64 kHz, the RMS current is measured over the first 15 μ s following the wakeup event. For the remaining time of the wakeup period, the current is similar to the Run mode current.

Table 21. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions		Typ ⁽¹⁾	Max ⁽¹⁾⁽²⁾	Unit
I_{DD} (Standby with RTC)	Supply current in Standby mode with RTC enabled	RTC clocked by LSI (no independent watchdog)	$T_A = -40$ °C to 25 °C $V_{DD} = 1.8$ V	0.9		μ A
			$T_A = -40$ °C to 25 °C	1.1	1.8	
			$T_A = 55$ °C	1.42	2.5	
			$T_A = 85$ °C	1.87	3	
		RTC clocked by LSE (no independent watchdog) ⁽³⁾	$T_A = -40$ °C to 25 °C $V_{DD} = 1.8$ V	1		
			$T_A = -40$ °C to 25 °C	1.33	2.9	
			$T_A = 55$ °C	1.59	3.4	
			$T_A = 85$ °C	2.01	4.3	
I_{DD} (Standby)	Supply current in Standby mode with RTC disabled	Independent watchdog and LSI enabled	$T_A = -40$ °C to 25 °C	1.1	1.6	
		Independent watchdog and LSI OFF	$T_A = -40$ °C to 25 °C	0.3	0.55	
			$T_A = 55$ °C	0.5	0.8	
			$T_A = 85$ °C	1	1.7	
I_{DD} (WU from Standby)	RMS supply current during wakeup time when exiting from Standby mode		$V_{DD} = 3.0$ V $T_A = -40$ °C to 25 °C	1		

1. The typical values are given for $V_{DD} = 3.0$ V and max values are given for $V_{DD} = 3.6$ V, unless otherwise specified.
2. Based on characterization, not tested in production, unless otherwise specified.
3. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8pF loading capacitors.

Wakeup time from Low power mode

The wakeup times given in the following table are measured with the MSI RC oscillator. The clock source used to wake up the device depends on the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode
- Stop mode: the clock source is the MSI oscillator in the range configured before entering Stop mode
- Standby mode: the clock source is the MSI oscillator running at 2.1 MHz

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 12](#).

Table 22. Typical and maximum timings in Low power modes

Symbol	Parameter	Conditions	Typ	Max ⁽¹⁾	Unit
$t_{WUSLEEP}$	Wakeup from Sleep mode	$f_{HCLK} = 32 \text{ MHz}$	0.36		μs
$t_{WUSLEEP_LP}$	Wakeup from Low power sleep mode $f_{HCLK} = 262 \text{ kHz}$	$f_{HCLK} = 262 \text{ kHz}$ Flash enabled	32		
		$f_{HCLK} = 262 \text{ kHz}$ Flash switched OFF	34		
t_{WUSTOP}	Wakeup from Stop mode, regulator in Run mode	$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$	8.2		
		$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ Voltage range 1 and 2	8.2	9.3	
	Wakeup from Stop mode, regulator in low power mode	$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ Voltage range 3	7.8	11.2	
		$f_{HCLK} = f_{MSI} = 2.1 \text{ MHz}$	10	12	
		$f_{HCLK} = f_{MSI} = 1.05 \text{ MHz}$	15.5	20	
		$f_{HCLK} = f_{MSI} = 524 \text{ kHz}$	29	35	
		$f_{HCLK} = f_{MSI} = 262 \text{ kHz}$	53	63	
		$f_{HCLK} = f_{MSI} = 131 \text{ kHz}$	105	118	
		$f_{HCLK} = f_{MSI} = 65 \text{ kHz}$	210	237	
$t_{WUSTDBY}$	Wakeup from Standby mode FWU bit = 1	$f_{HCLK} = f_{MSI} = 2.1 \text{ MHz}$	50	103	ms
	Wakeup from Standby mode FWU bit = 0	$f_{HCLK} = f_{MSI} = 2.1 \text{ MHz}$	2.5	3.2	

1. Based on characterization, not tested in production, unless otherwise specified

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following table. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked off
 - with only one peripheral clocked on

Table 23. Peripheral current consumption⁽¹⁾

Peripheral		Typical consumption, $V_{DD} = 3.0\text{ V}$, $T_A = 25\text{ °C}$				Unit
		Range 1, $V_{CORE} = 1.8\text{ V}$ $VOS[1:0] = 01$	Range 2, $V_{CORE} = 1.5\text{ V}$ $VOS[1:0] = 10$	Range 3, $V_{CORE} = 1.2\text{ V}$ $VOS[1:0] = 11$	Low power sleep and run	
APB1	TIM2	13	10.5	8	10.5	$\mu\text{A/MHz}$ (f_{HCLK})
	TIM3	14	12	9	12	
	TIM4	12.5	10.5	8	11	
	TIM6	5.5	4.5	3.5	4.5	
	TIM7	5.5	5	3.5	4.5	
	LCD	5.5	5	3.5	5	
	WWDG	4	3.5	2.5	3.5	
	SPI2	5.5	5	4	5	
	USART2	9	8	5.5	8.5	
	USART3	10.5	9	6	8	
	I2C1	8.5	7	5.5	7.5	
	I2C2	8.5	7	5.5	6.5	
	USB	12.5	10	6.5	10	
	PWR	4.5	4	3	3.5	
	DAC	9	7.5	6	7	
	COMP	4.5	4	3.5	4.5	

Table 23. Peripheral current consumption⁽¹⁾ (continued)

Peripheral		Typical consumption, V _{DD} = 3.0 V, T _A = 25 °C				Unit
		Range 1, V _{CORE} = 1.8 V VOS[1:0] = 01	Range 2, V _{CORE} = 1.5 V VOS[1:0] = 10	Range 3, V _{CORE} = 1.2 V VOS[1:0] = 11	Low power sleep and run	
APB2	SYSCFG & RI	3	2.5	2	2.5	μA/MHz (f _{HCLK})
	TIM9	9	7.5	6	7	
	TIM10	6.5	5.5	4.5	5.5	
	TIM11	7	6	4.5	5.5	
	ADC ⁽²⁾	11.5	9.5	8	9	
	SPI1	5	4.5	3	4	
	USART1	9	7.5	6	7.5	
AHB	GPIOA	5	4.5	3.5	4	
	GPIOB	5	4.5	3.5	4.5	
	GPIOC	5	4.5	3.5	4.5	
	GPIOD	5	4.5	3.5	4.5	
	GPIOE	5	4.5	3.5	4.5	
	GPIOH	4	4	3	3.5	
	CRC	1	0.5	0.5	0.5	
	FLASH	13	11.5	9	18.5	
	DMA1	12	10	8	10.5	
All enabled		166	138	106	130	
I _{DD} (RTC)		0.47				μA
I _{DD} (LCD)		3.1				
I _{DD} (ADC) ⁽³⁾		1450				
I _{DD} (DAC) ⁽⁴⁾		340				
I _{DD} (COMP1)		0.16				
I _{DD} (COMP2)	Slow mode	2				
	Fast mode	5				
I _{DD} (PVD / BOR) ⁽⁵⁾		2.6				
I _{DD} (IWDG)		0.25				

1. Data based on differential I_{DD} measurement between all peripherals OFF and one peripheral with clock enabled, in the following conditions: $f_{HCLK} = 32\text{ MHz}$ (range 1), $f_{HCLK} = 16\text{ MHz}$ (range 2), $f_{HCLK} = 4\text{ MHz}$ (range 3), $f_{HCLK} = 64\text{ kHz}$ (Low power run/sleep), $f_{APB1} = f_{HCLK}$, $f_{APB2} = f_{HCLK}$, default prescaler value for each peripheral. The CPU is in Sleep mode in both cases. No I/O pins toggling. Not tested in production.

2. HSI oscillator is OFF for this measure.

3. Data based on a differential I_{DD} measurement between ADC in reset configuration and continuous ADC conversion (HSI consumption not included).

4. Data based on a differential I_{DD} measurement between DAC in reset configuration and continuous DAC conversion of V_{DD}/2. DAC is in buffered mode, output is left floating.
5. Including supply current of internal reference voltage.

6.3.5 External clock source characteristics

High-speed external user clock generated from an external source

Table 24. High-speed external user clock characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f _{HSE_ext}	User external clock source frequency		1	8	32	MHz
V _{HSEH}	OSC_IN input pin high level voltage		0.7V _{DD}		V _{DD}	V
V _{HSEL}	OSC_IN input pin low level voltage		V _{SS}		0.3V _{DD}	
t _{w(HSE)} t _{w(HSE)}	OSC_IN high or low time		12			ns
t _{r(HSE)} t _{f(HSE)}	OSC_IN rise or fall time				20	
C _{in(HSE)}	OSC_IN input capacitance			2.6		pF
DuCy _(HSE)	Duty cycle		45		55	%
I _L	OSC_IN Input leakage current	V _{SS} ≤ V _{IN} ≤ V _{DD}			±1	μA

1. Guaranteed by design, not tested in production.

Low-speed external user clock generated from an external source

The characteristics given in the following table result from tests performed using a low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 12](#).

Table 25. Low-speed external user clock characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User external clock source frequency		1	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$		V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}		$0.3V_{DD}$	
$t_{w(LSE)}$ $t_{w(LSE)}$	OSC32_IN high or low time		465	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time		-	-	10	
$C_{IN(LSE)}$	OSC32_IN input capacitance		-	0.6	-	pF
$DuCy_{(LSE)}$	Duty cycle		45	-	55	%
I_L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	± 1	μA

1. Guaranteed by design, not tested in production

Figure 10. Low-speed external clock source AC timing diagram

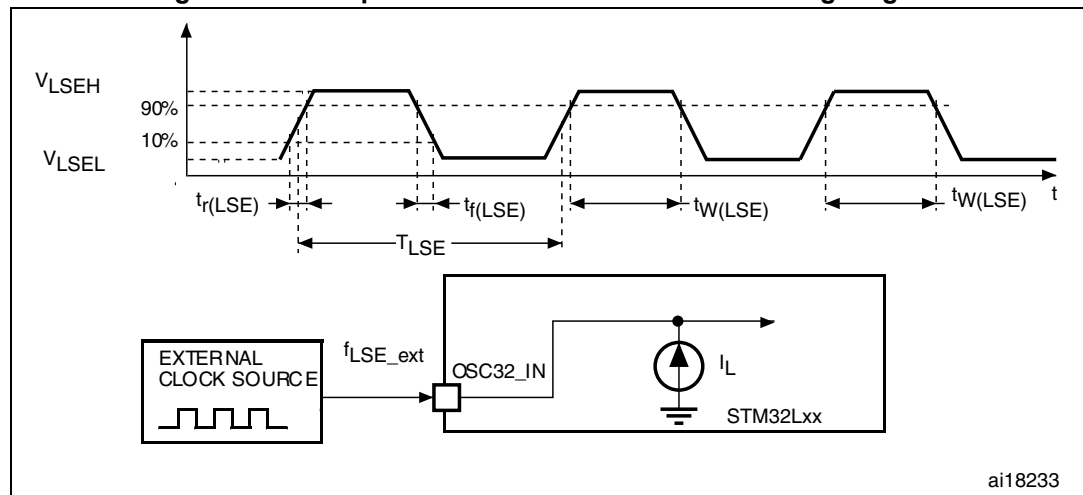
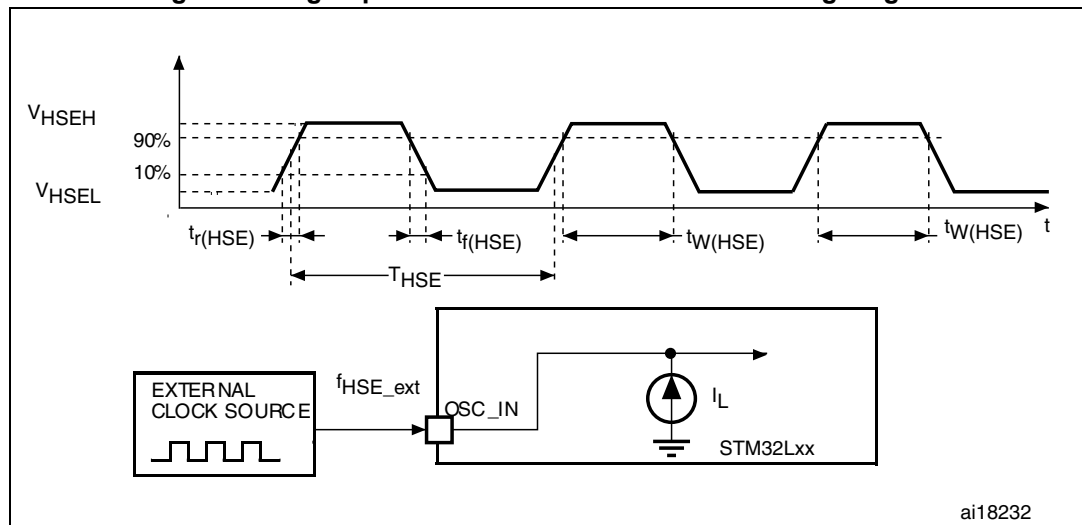


Figure 11. High-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 24 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 26](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

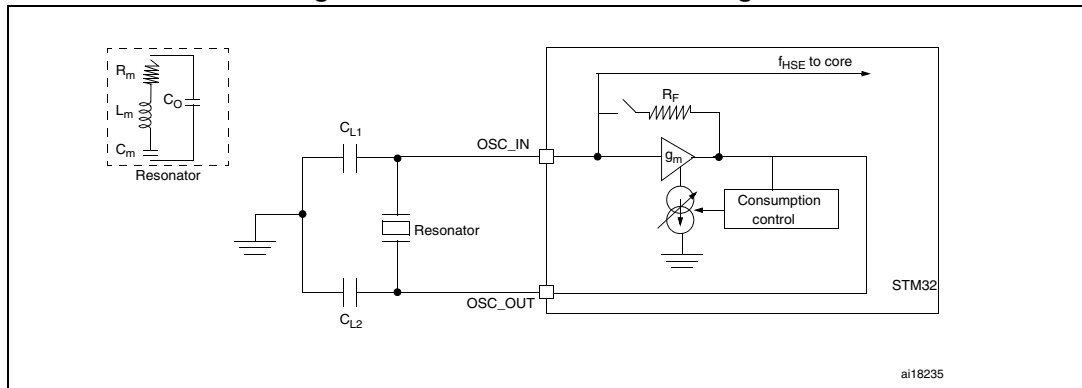
Table 26. HSE 1-24 MHz oscillator characteristics⁽¹⁾⁽²⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency		1		24	MHz
R_F	Feedback resistor			200		k Ω
C	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S) ⁽³⁾	$R_S = 30 \Omega$		20		pF
I_{HSE}	HSE driving current	$V_{DD} = 3.3 V$, $V_{IN} = V_{SS}$ with 30 pF load			3	mA
$I_{DD(HSE)}$	HSE oscillator power consumption	C = 20 pF $f_{OSC} = 16$ MHz			2.5 (startup) 0.7 (stabilized)	mA
		C = 10 pF $f_{OSC} = 16$ MHz			2.5 (startup) 0.46 (stabilized)	
g_m	Oscillator transconductance	Startup	3.5			mA/ V
$t_{SU(HSE)}^{(4)}$	Startup time	V_{DD} is stabilized		1		ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Based on characterization results, not tested in production.
3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see [Figure 12](#)). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} . Refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 12. HSE oscillator circuit diagram



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 27](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 27. LSE oscillator characteristics ($f_{LSE} = 32.768 \text{ kHz}$)⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE}	Low speed external oscillator frequency			32.768		kHz
R_F	Feedback resistor			1.2		MΩ
$C^{(2)}$	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S) ⁽³⁾	$R_S = 30 \text{ k}\Omega$		8		pF
I_{LSE}	LSE driving current	$V_{DD} = 3.3 \text{ V}$, $V_{IN} = V_{SS}$			1.1	μA
$I_{DD} \text{ (LSE)}$	LSE oscillator current consumption	$V_{DD} = 1.8 \text{ V}$		450		nA
		$V_{DD} = 3.0 \text{ V}$		600		
		$V_{DD} = 3.6 \text{ V}$		750		
g_m	Oscillator transconductance		3			μA/V
$t_{SU(LSE)}^{(4)}$	Startup time	V_{DD} is stabilized		1		s

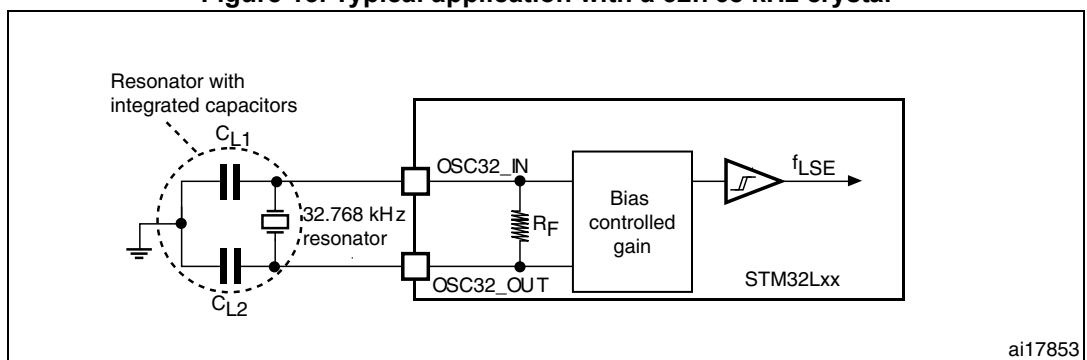
1. Based on characterization, not tested in production.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".
3. The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R_S value for example MSIV-TIN32.768kHz. Refer to crystal manufacturer for more details;
4. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Note: For C_{L1} and C_{L2} , it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator (see [Figure 13](#)). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

Caution: To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF) it is strongly recommended to use a resonator with a load capacitance $C_L \leq 7$ pF. Never use a resonator with a load capacitance of 12.5 pF.

Example: if you choose a resonator with a load capacitance of $C_L = 6$ pF and $C_{stray} = 2$ pF, then $C_{L1} = C_{L2} = 8$ pF.

Figure 13. Typical application with a 32.768 kHz crystal



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6.3.6 Internal clock source characteristics

The parameters given in the following table are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 12](#).

High-speed internal (HSI) RC oscillator

Table 28. HSI oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	$V_{DD} = 3.0\text{ V}$		16		MHz
$TRIM^{(1)(2)}$	HSI user-trimmed resolution	Trimming code is not a multiple of 16		± 0.4	0.7	%
		Trimming code is a multiple of 16			± 1.5	%
$ACC_{HSI}^{(2)}$		$V_{DDA} = 1.8\text{ V to }3.6\text{ V}$ $T_A = -40\text{ to }85\text{ }^{\circ}\text{C}$	-10		+10	%
$t_{SU(HSI)}^{(2)}$	HSI oscillator startup time			3.7	6	μs
$I_{DD(HSI)}^{(2)}$	HSI oscillator power consumption			100	140	μA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Based on characterization, not tested in production.

Low-speed internal (LSI) RC oscillator

Table 29. LSI oscillator characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$f_{LSI}^{(1)}$	LSI frequency	26	38	56	kHz
$D_{LSI}^{(2)}$	LSI oscillator frequency drift $0^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$	-10		4	%
$t_{SU(LSI)}^{(3)}$	LSI oscillator startup time			200	μs
$I_{DD(LSI)}^{(3)}$	LSI oscillator power consumption		400	510	nA

1. Tested in production.
2. This is a deviation for an individual part, once the initial frequency has been measured.
3. Guaranteed by design, not tested in production.

Multi-speed internal (MSI) RC oscillator

Table 30. MSI oscillator characteristics

Symbol	Parameter	Condition	Typ	Max	Unit
f_{MSI}	Frequency after factory calibration, done at $V_{\text{DD}} = 3.3 \text{ V}$ and $T_{\text{A}} = 25 \text{ }^{\circ}\text{C}$	MSI range 0	65.5		kHz
		MSI range 1	131		
		MSI range 2	262		
		MSI range 3	524		
		MSI range 4	1.05		MHz
		MSI range 5	2.1		
		MSI range 6	4.2		
ACC_{MSI}	Frequency error after factory calibration		± 0.5		%
$D_{\text{TEMP}(\text{MSI})}^{(1)}$	MSI oscillator frequency drift $0 \text{ }^{\circ}\text{C} \leq T_{\text{A}} \leq 85 \text{ }^{\circ}\text{C}$		± 10		%
$D_{\text{VOLT}(\text{MSI})}^{(1)}$	MSI oscillator frequency drift $1.8 \text{ V} \leq V_{\text{DD}} \leq 3.6 \text{ V}$, $T_{\text{A}} = 25 \text{ }^{\circ}\text{C}$			2.5	%/V
$I_{\text{DD}(\text{MSI})}^{(2)}$	MSI oscillator power consumption	MSI range 0	0.75		μA
		MSI range 1	1		
		MSI range 2	1.5		
		MSI range 3	2.5		
		MSI range 4	4.5		
		MSI range 5	8		
		MSI range 6	15		
$t_{\text{SU}(\text{MSI})}$	MSI oscillator startup time	MSI range 0	30		μs
		MSI range 1	20		
		MSI range 2	15		
		MSI range 3	10		
		MSI range 4	6		
		MSI range 5	5		
		MSI range 6, Voltage range 1 and 2	3.5		
		MSI range 6, Voltage range 3	5		

Table 30. MSI oscillator characteristics (continued)

Symbol	Parameter	Condition	Typ	Max	Unit
$t_{\text{STAB(MSI)}}^{(2)}$	MSI oscillator stabilization time	MSI range 0		40	μs
		MSI range 1		20	
		MSI range 2		10	
		MSI range 3		4	
		MSI range 4		2.5	
		MSI range 5		2	
		MSI range 6, Voltage range 1 and 2		2	
		MSI range 3, Voltage range 3		3	
$f_{\text{OVER(MSI)}}$	MSI oscillator frequency overshoot	Any range to range 5		4	MHz
		Any range to range 6		6	

1. This is a deviation for an individual part, once the initial frequency has been measured.

2. Based on characterization, not tested in production.

6.3.7 PLL characteristics

The parameters given in [Table 31](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 12](#).

Table 31. PLL characteristics

Symbol	Parameter	Value			Unit
		Min	Typ	Max ⁽¹⁾	
$f_{\text{PLL_IN}}$	PLL input clock ⁽²⁾	2		24	MHz
	PLL input clock duty cycle	45		55	%
$f_{\text{PLL_OUT}}$	PLL output clock	2		32	MHz
t_{LOCK}	Worst case PLL lock time PLL input = 2 MHz PLL VCO = 96 MHz		100	130	μs
Jitter	Cycle-to-cycle jitter			± 600	ps
$I_{\text{DDA(PLL)}}$	Current consumption on V_{DDA}		220	450	μA
$I_{\text{DD(PLL)}}$	Current consumption on V_{DD}		120	150	

1. Based on characterization, not tested in production.

2. Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by $f_{\text{PLL_OUT}}$.

6.3.8 Memory characteristics

The characteristics are given at $T_A = -40$ to 85 °C unless otherwise specified.

RAM memory

Table 32. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
VRM	Data retention mode ⁽¹⁾	STOP mode (or RESET)	1.8			V

1. Minimum supply voltage without losing data stored in RAM (in Stop mode or under Reset) or in hardware registers (only in Stop mode).

Flash memory and data EEPROM

Table 33. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Typ	Max ⁽¹⁾	Unit
V_{DD}	Operating voltage Read / Write / Erase		1.8		3.6	V
t_{prog}	Programming time for word or half-page	Erasing		3.28	3.94	ms
		Programming		3.28	3.94	
I_{DD}	Average current during whole programme/erase operation	$T_A = 25$ °C, $V_{DD} = 3.6$ V		300		μ A
	Maximum current (peak) during programme/erase operation			1.5	2.5	mA

1. Guaranteed by design, not tested in production.

Table 34. Flash memory, data EEPROM endurance and data retention

Symbol	Parameter	Conditions	Value			Unit
			Min ⁽¹⁾	Typ	Max	
N _{CYC} ⁽²⁾	Cycling (erase / write) Program memory	T _A = -40°C to 85 °C	1			kcycles
	Cycling (erase / write) EEPROM data memory		100			
t _{RET} ⁽²⁾	Data retention (program memory) after 1 kcycle at T _A = 85 °C	T _{RET} = +85 °C	10			years
	Data retention (EEPROM data memory) after 100 kcycles at T _A = 85 °C		10			

1. Based on characterization not tested in production.

2. Characterization is done according to JEDEC JESD22-A117.

6.3.9 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB: A Burst of Fast Transient voltage** (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in [Table 35](#). They are based on the EMS levels and classes defined in application note AN1709.

Table 35. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V _{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V _{DD} = 3.3 V, LQFP100, T _A = +25 °C, f _{HCLK} = 32 MHz conforms to IEC 61000-4-2	2B
V _{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V _{DD} and V _{SS} pins to induce a functional disturbance	V _{DD} = 3.3 V, LQFP100, T _A = +25 °C, f _{HCLK} = 32 MHz conforms to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 36. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. frequency range			Unit
				4 MHz voltage range 3	16 MHz voltage range 2	32 MHz voltage range 1	
S _{EMI}	Peak level	V _{DD} = 3.3 V, T _A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 to 30 MHz	3	-6	-5	dBμV
			30 to 130 MHz	18	4	-7	
			130 MHz to 1GHz	15	5	-7	
			SAE EMI Level	2.5	2	1	-

6.3.10 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts $\times$ (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 37. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
$V_{\text{ESD(HBM)}}$	Electrostatic discharge voltage (human body model)	$T_A = +25\text{ }^{\circ}\text{C}$, conforming to JESD22-A114	2	2000	V
$V_{\text{ESD(CDM)}}$	Electrostatic discharge voltage (charge device model)	$T_A = +25\text{ }^{\circ}\text{C}$, conforming to JESD22-C101	II	500	

1. Based on characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 38. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +85\text{ }^{\circ}\text{C}$ conforming to JESD78A	II level A

6.3.11 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error, out of spec current injection on adjacent pins or other functional failure (for example reset, oscillator frequency deviation, LCD levels, etc.).

The test results are given in the following table.

Table 39. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I _{INJ}	Injected current on true open-drain pins	-5	+0	mA
	Injected current on all 5 V tolerant (FT) pins	-5	+0	
	Injected current on any other pin	-5	+5	

6.3.12 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in [Table 40](#) are derived from tests performed under conditions summarized in [Table 12](#). All I/Os are CMOS and TTL compliant.

Table 40. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage	TTL ports $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$	$V_{SS} - 0.3$		0.8	V
V_{IH}	Standard I/O input high level voltage		2 ⁽¹⁾		$V_{DD} + 0.3$	
	FT ⁽²⁾ I/O input high level voltage				5.5V	
V_{IL}	Input low level voltage	CMOS ports $1.8\text{ V} \leq V_{DD} \leq 3.6\text{ V}$	-0.3		$0.3V_{DD}$ ⁽³⁾	V
V_{IH}	Standard I/O Input high level voltage	CMOS ports $1.8\text{ V} \leq V_{DD} \leq 3.6\text{ V}$	0.7 V_{DD} ⁽³⁾⁽⁴⁾		$V_{DD} + 0.3$	
	FT ⁽⁵⁾ I/O input high level voltage	CMOS ports $1.8\text{ V} \leq V_{DD} \leq 2.0\text{ V}$			5.25	
		CMOS ports $2.0\text{ V} \leq V_{DD} \leq 3.6\text{ V}$			5.5	
V_{hys}	Standard I/O Schmitt trigger voltage hysteresis ⁽⁶⁾		10% V_{DD} ⁽⁷⁾			
I_{lk}	Input leakage current ⁽⁸⁾⁽³⁾	$V_{SS} \leq V_{IN} \leq V_{DD}$ I/Os with LCD			±50	nA
		$V_{SS} \leq V_{IN} \leq V_{DD}$ I/Os with analog switches			±50	
		$V_{SS} \leq V_{IN} \leq V_{DD}$ I/Os with analog switches and LCD			±50	
		$V_{SS} \leq V_{IN} \leq V_{DD}$ I/Os with USB			TBD	
		$V_{SS} \leq V_{IN} \leq V_{DD}$ Standard I/Os			±50	
R_{PU}	Weak pull-up equivalent resistor ⁽⁹⁾⁽³⁾	$V_{IN} = V_{SS}$	30	45	60	kΩ
R_{PD}	Weak pull-down equivalent resistor ⁽⁹⁾⁽³⁾	$V_{IN} = V_{DD}$	30	45	60	kΩ
C_{IO}	I/O pin capacitance			5		pF

1. Guaranteed by design.
2. FT = 5V tolerant. To sustain a voltage higher than $V_{DD} + 0.5$ the internal pull-up/pull-down resistors must be disabled.
3. Tested in production
4. $0.7V_{DD}$ for 5V-tolerant receiver
5. FT = Five-volt tolerant.
6. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization, not tested in production.
7. With a minimum of 200 mV. Based on characterization, not tested in production.
8. The max. value may be exceeded if negative current is injected on adjacent pins.
9. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This MOS/NMOS contribution to the series resistance is minimum (~10% order).

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 20 mA (with the non-standard V_{OL}/V_{OH} specifications given in [Table 41](#)).

in the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in [Section 6.2](#):

- The sum of the currents sourced by all the I/Os on V_{DD} , plus the maximum Run consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating I_{VDD} (see [Table 10](#)).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating I_{VSS} (see [Table 10](#)).

Output voltage levels

Unless otherwise specified, the parameters given in [Table 41](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 12](#). All I/Os are CMOS and TTL compliant.

Table 41. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{OL}^{(1)(2)}$	Output low level voltage for an I/O pin when 8 pins are sunk at same time	$I_{IO} = +8$ mA 2.7 V < V_{DD} < 3.6 V		0.4	V
$V_{OH}^{(3)(2)}$	Output high level voltage for an I/O pin when 8 pins are sourced at same time		2.4		
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin when 8 pins are sunk at same time	$I_{IO} = +4$ mA 1.8 V < V_{DD} < 2.7 V		0.45	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin when 8 pins are sourced at same time		$V_{DD}-0.45$		
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin when 4 pins are sunk at same time	$I_{IO} = +20$ mA 2.7 V < V_{DD} < 3.6 V		1.3	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin when 4 pins are sourced at same time		$V_{DD}-1.3$		

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in [Table 10](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS} .
2. Tested in production.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in [Table 10](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD} .
4. Based on characterization data, not tested in production.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in [Figure 14](#) and [Table 42](#), respectively.

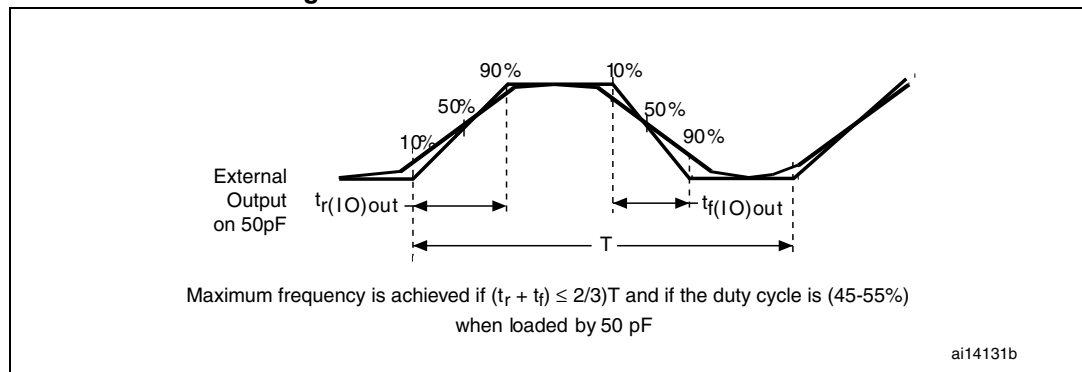
Unless otherwise specified, the parameters given in [Table 42](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 12](#).

Table 42. I/O AC characteristics⁽¹⁾

OSPEEDRx [1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Max ⁽²⁾	Unit
00	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	400	kHz
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	400	
	$t_{f(\text{IO})\text{out}}$ $t_{r(\text{IO})\text{out}}$	Output rise and fall time	$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	625	ns
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	625	
01	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	2	MHz
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	1	
	$t_{f(\text{IO})\text{out}}$ $t_{r(\text{IO})\text{out}}$	Output rise and fall time	$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	125	ns
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	250	
10	$F_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	10	MHz
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	2	
	$t_{f(\text{IO})\text{out}}$ $t_{r(\text{IO})\text{out}}$	Output rise and fall time	$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	25	ns
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	125	
11	$F_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	50	MHz
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	8	
	$t_{f(\text{IO})\text{out}}$ $t_{r(\text{IO})\text{out}}$	Output rise and fall time	$C_L = 30 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	5	ns
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	30	
-	$t_{\text{EXTI}pw}$	Pulse width of external signals detected by the EXTI controller		8	-	ns

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the STM32L100xx reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design. Not tested in production.
3. The maximum frequency is defined in [Figure 14](#).

Figure 14. I/O AC characteristics definition



6.3.13 NRST pin characteristics

The NRST pin input driver uses CMOS technology.

Unless otherwise specified, the parameters given in [Table 43](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 12](#).

Table 43. NRST pin characteristics

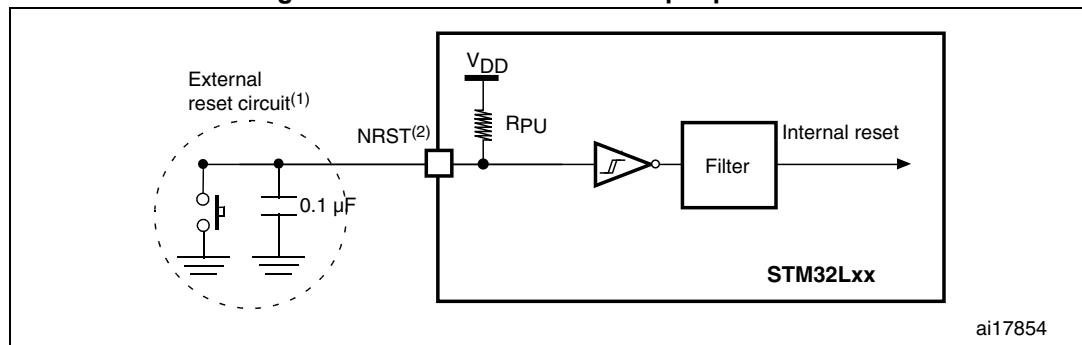
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}^{(1)}$	NRST input low level voltage		V_{SS}		0.8	V
$V_{IH(NRST)}^{(1)}$	NRST input high level voltage		1.4		V_{DD}	
$V_{OL(NRST)}^{(1)}$	NRST output low level voltage	$I_{OL} = 2\text{ mA}$ $2.7\text{ V} < V_{DD} < 3.6\text{ V}$			0.4	
		$I_{OL} = 1.5\text{ mA}$ $1.8\text{ V} < V_{DD} < 2.7\text{ V}$				
$V_{hys(NRST)}^{(1)}$	NRST Schmitt trigger voltage hysteresis		$10\%V_{DD}^{(2)}$			mV
R_{PU}	Weak pull-up equivalent resistor ⁽³⁾	$V_{IN} = V_{SS}$	30	45	60	kΩ
$V_{F(NRST)}^{(1)}$	NRST input filtered pulse				50	ns
$V_{NF(NRST)}^{(1)}$	NRST input not filtered pulse		350			ns

1. Guaranteed by design, not tested in production.

2. 200 mV minimum value

3. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.

Figure 15. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 43](#). Otherwise the reset will not be taken into account by the device.

6.3.14 TIM timer characteristics

The parameters given in the following table are guaranteed by design.

Refer to [Section 6.3.11: I/O current injection characteristics](#) for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 44. TIMx⁽¹⁾ characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time		1		$t_{TIMxCLK}$
		$f_{TIMxCLK} = 32 \text{ MHz}$	31.25		ns
f_{EXT}	Timer external clock frequency on CH1 to CH4		0	$f_{TIMxCLK}/2$	MHz
		$f_{TIMxCLK} = 32 \text{ MHz}$	0	16	MHz
Res_{TIM}	Timer resolution			16	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected (timer's prescaler disabled)		1	65536	$t_{TIMxCLK}$
		$f_{TIMxCLK} = 32 \text{ MHz}$	0.0312	2048	µs
t_{MAX_COUNT}	Maximum possible count			65536×65536	$t_{TIMxCLK}$
		$f_{TIMxCLK} = 32 \text{ MHz}$		134.2	s

1. TIMx is used as a general term to refer to the TIM1, TIM2, TIM3 and TIM4 timers.

6.3.15 Communication interfaces

I²C interface characteristics

Unless otherwise specified, the parameters given in [Table 45](#) are derived from tests performed under ambient temperature, fPCLK1 frequency and VDD supply voltage conditions summarized in [Table 12](#).

The STM32L100C6 product line I²C interface meets the requirements of the standard I²C communication protocol with the following restrictions: SDA and SCL are not “true” open-drain I/O pins. When configured as open-drain, the PMOS connected between the I/O pin and VDD is disabled, but is still present.

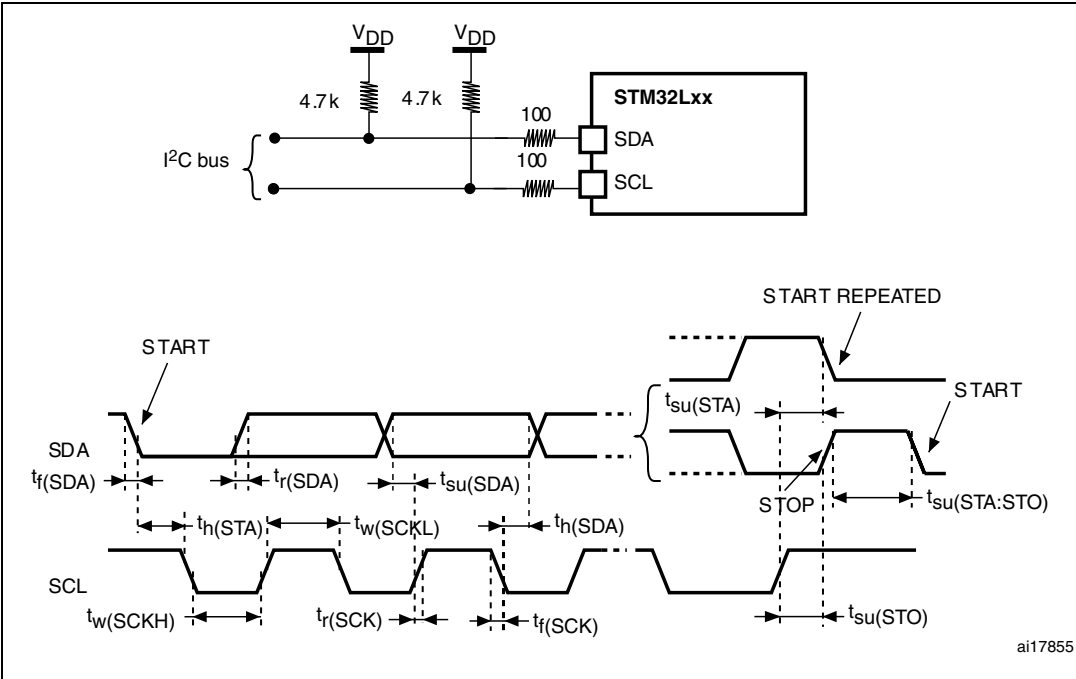
The I²C characteristics are described in [Table 45](#). Refer also to [Section 6.3.11: I/O current injection characteristics](#) for more details on the input/output alternate function characteristics (SDA and SCL).

Table 45. I²C characteristics

Symbol	Parameter	Standard mode I ² C ⁽¹⁾		Fast mode I ² C ⁽¹⁾⁽²⁾		Unit
		Min	Max	Min	Max	
t _w (SCLL)	SCL clock low time	4.7		1.3		μs
t _w (SCLH)	SCL clock high time	4.0		0.6		
t _{su} (SDA)	SDA setup time	250		100		ns
t _h (SDA)	SDA data hold time	0		0	900 ⁽³⁾	
t _r (SDA) t _r (SCL)	SDA and SCL rise time		1000	20 + 0.1C _b	300	
t _f (SDA) t _f (SCL)	SDA and SCL fall time		300		300	
t _h (STA)	Start condition hold time	4.0		0.6		μs
t _{su} (STA)	Repeated Start condition setup time	4.7		0.6		
t _{su} (STO)	Stop condition setup time	4.0		0.6		μs
t _w (STO:STA)	Stop to Start condition time (bus free)	4.7		1.3		μs
C _b	Capacitive load for each bus line		400		400	pF

1. Guaranteed by design, not tested in production.
2. f_{PCLK1} must be at least 2 MHz to achieve standard mode I²C frequencies. It must be at least 4 MHz to achieve fast mode I²C frequencies. It must be a multiple of 10 MHz to reach the 400 kHz maximum I²C fast mode clock.
3. The maximum Data hold time has only to be met if the interface does not stretch the low period of SCL signal.

Figure 16. I²C bus AC waveforms and measurement circuit



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Table 46. SCL frequency ($f_{PCLK1} = 32 \text{ MHz}$, $V_{DD} = 3.3 \text{ V}$)⁽¹⁾⁽²⁾

f_{SCL} (kHz)	I2C_CCR value
	$R_P = 4.7 \text{ k}\Omega$
400	0x801B
300	0x8024
200	0x8035
100	0x00A0
50	0x0140
20	0x0320

- R_P = External pull-up resistance, f_{SCL} = I²C speed.
- For speeds around 200 kHz, the tolerance on the achieved speed is of $\pm 5\%$. For other speed ranges, the tolerance on the achieved speed is $\pm 2\%$. These variations depend on the accuracy of the external components used to design the application.

SPI characteristics

Unless otherwise specified, the parameters given in the following table are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 12](#).

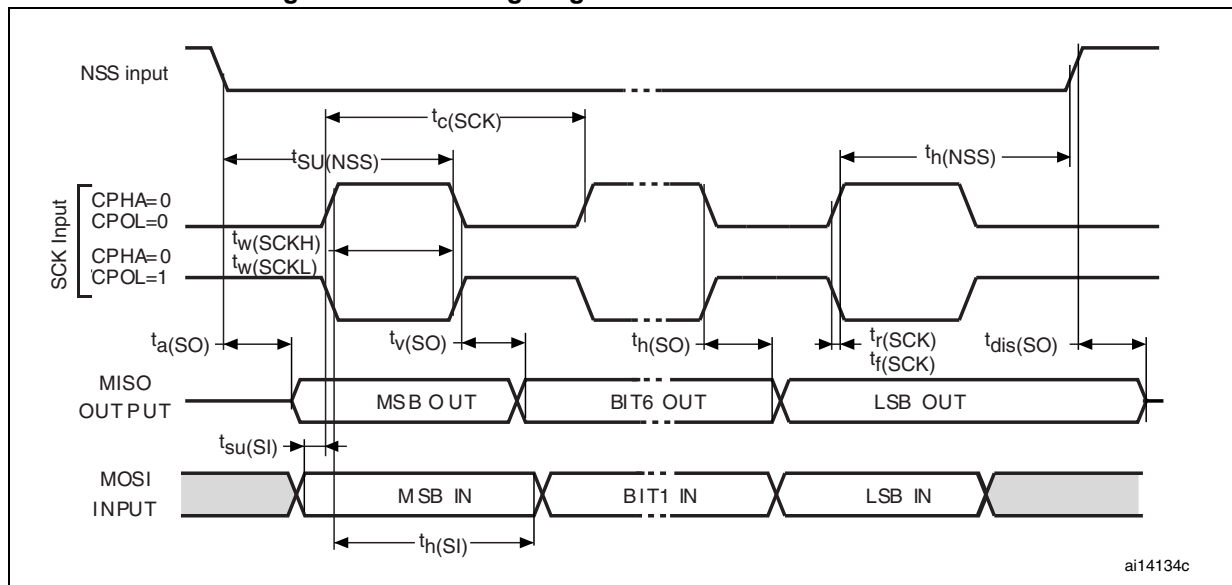
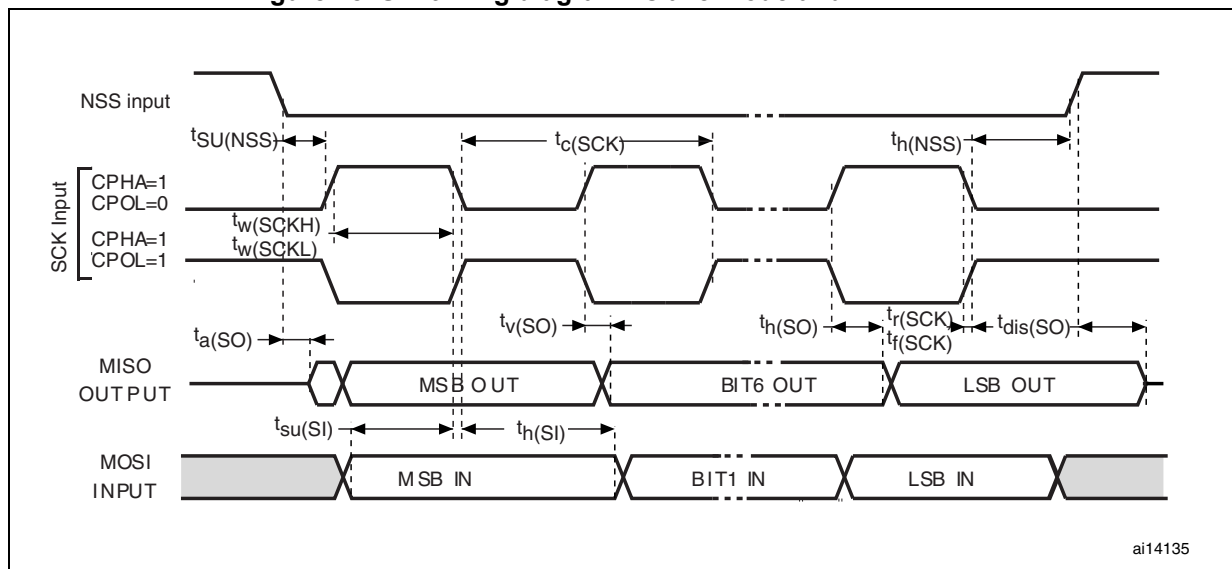
Refer to [Section 6.3.11: I/O current injection characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 47. SPI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max ⁽²⁾	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	16	MHz
		Slave mode	-	16	
		Slave transmitter	-	12 ⁽³⁾	
$t_{r(SCK)}^{(2)}$ $t_{f(SCK)}^{(2)}$	SPI clock rise and fall time	Capacitive load: C = 30 pF	-	6	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode	$4t_{HCLK}$	-	ns
$t_h(NSS)$	NSS hold time	Slave mode	$2t_{HCLK}$	-	
$t_{w(SCKH)}^{(2)}$ $t_{w(SCKL)}^{(2)}$	SCK high and low time	Master mode	$t_{SCK}/2 - 5$	$t_{SCK}/2 + 3$	
$t_{su(MI)}^{(2)}$	Data input setup time	Master mode	5	-	
$t_{su(SI)}^{(2)}$		Slave mode	6	-	
$t_{h(MI)}^{(2)}$	Data input hold time	Master mode	5	-	
$t_{h(SI)}^{(2)}$		Slave mode	5	-	
$t_{a(SO)}^{(4)}$	Data output access time	Slave mode	0	$3t_{HCLK}$	
$t_{v(SO)}^{(2)}$	Data output valid time	Slave mode	-	33	
$t_{v(MO)}^{(2)}$	Data output valid time	Master mode	-	6.5	
$t_{h(SO)}^{(2)}$	Data output hold time	Slave mode	17	-	
$t_{h(MO)}^{(2)}$		Master mode	0.5	-	

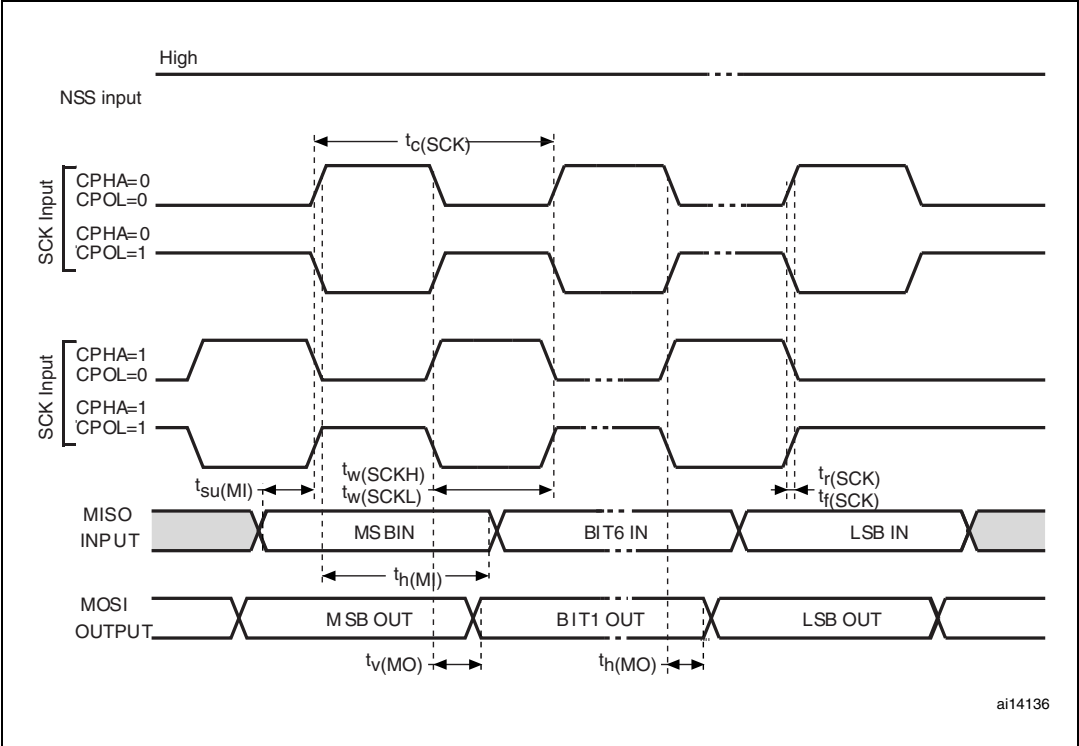
1. The characteristics above are given for voltage range 1.
2. Based on characterization, not tested in production.
3. The maximum SPI clock frequency in slave transmitter mode is given for an SPI slave input clock duty cycle (DuCy(SCK)) ranging between 40 to 60%.
4. Min time is for the minimum time to drive the output and max time is for the maximum time to validate the data.

Figure 17. SPI timing diagram - slave mode and CPHA = 0

Figure 18. SPI timing diagram - slave mode and CPHA = 1⁽¹⁾

1. Measurement points are done at CMOS levels: 0.3V_{DD} and 0.7V_{DD}.

Figure 19. SPI timing diagram - master mode⁽¹⁾



1. Measurement points are done at CMOS levels: 0.3V_{DD} and 0.7V_{DD}.

USB characteristics

The USB interface is USB-IF certified (full speed).

Table 48. USB startup time

Symbol	Parameter	Max	Unit
t _{STARTUP} ⁽¹⁾	USB transceiver startup time	1	μs

1. Guaranteed by design, not tested in production.

Table 49. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input levels					
V _{DD}	USB operating voltage ⁽²⁾		3.0	3.6	V
V _{DI} ⁽³⁾	Differential input sensitivity	I(USB_DP, USB_DM)	0.2		V
V _{CM} ⁽³⁾	Differential common mode range	Includes V _{DI} range	0.8	2.5	
V _{SE} ⁽³⁾	Single ended receiver threshold		1.3	2.0	
Output levels					
V _{OL} ⁽⁴⁾	Static output level low	R _L of 1.5 kΩ to 3.6 V ⁽⁵⁾		0.3	V
V _{OH} ⁽⁴⁾	Static output level high	R _L of 15 kΩ to V _{SS} ⁽⁵⁾	2.8	3.6	

1. All the voltages are measured from the local ground potential.
2. To be compliant with the USB 2.0 full speed electrical specification, the USB_DP (D+) pin should be pulled up with a 1.5 k Ω resistor to a 3.0-to-3.6 V voltage range.
3. Guaranteed by characterization, not tested in production.
4. Tested in production.
5. R_L is the load connected on the USB drivers.

Figure 20. USB timings: definition of data signal rise and fall time

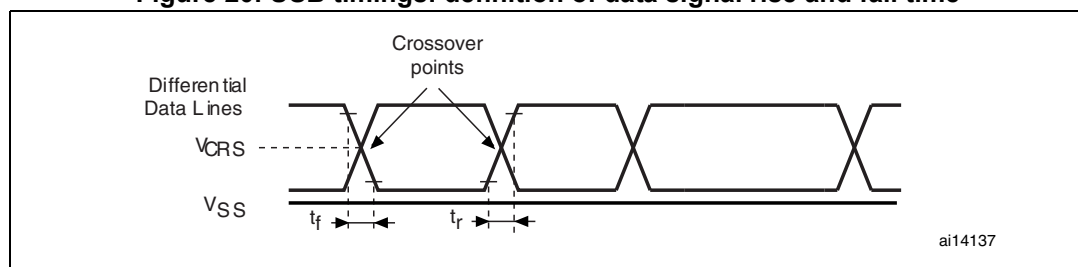


Table 50. USB: full speed electrical characteristics

Driver characteristics ⁽¹⁾					
Symbol	Parameter	Conditions	Min	Max	Unit
t_r	Rise time ⁽²⁾	$C_L = 50$ pF	4	20	ns
t_f	Fall Time ⁽²⁾	$C_L = 50$ pF	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage		1.3	2.0	V

1. Guaranteed by design, not tested in production.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

6.3.16 12-bit ADC characteristics

Unless otherwise specified, the parameters given in [Table 52](#) are guaranteed by design.

Table 51. ADC clock frequency

Symbol	Parameter	Conditions		Min	Max	Unit
f _{ADC}	ADC clock frequency	Voltage range 1 & 2	2.4 V ≤V _{DDA} ≤3.6 V	0.480	16	MHz
			1.8 V ≤V _{DDA} ≤2.4 V		8	
		Voltage range 3			4	

Table 52. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Power supply		1.8		3.6	V
$I_{\text{VDDA}}^{(1)}$	Current on the V_{DDA} input pin	Peak		1400	2150	μA
		Average			1900	
V_{AIN}	Conversion voltage range		0 ⁽²⁾		V_{DDA}	V
f_{S}	12-bit sampling rate	Direct channels	0.03		1	MSPS
		Multiplexed channels	0.03		0.76	
	10-bit sampling rate	Direct channels	0.03		1.07	MSPS
		Multiplexed channels	0.03		0.8	
	8-bit sampling rate	Direct channels	0.03		1.23	MSPS
		Multiplexed channels	0.03		0.89	
	6-bit sampling rate	Direct channels	0.03		1.45	MSPS
		Multiplexed channels	0.03		1	
t_{S}	Sampling time	Direct channels $2.4 \text{ V} \leq V_{\text{DDA}} \leq 3.6 \text{ V}$	0.25			μs
		Multiplexed channels $2.4 \text{ V} \leq V_{\text{DDA}} \leq 3.6 \text{ V}$	0.56			
		Direct channels $1.8 \text{ V} \leq V_{\text{DDA}} \leq 2.4 \text{ V}$	0.56			
		Multiplexed channels $1.8 \text{ V} \leq V_{\text{DDA}} \leq 2.4 \text{ V}$	1			
			4		384	$1/f_{\text{ADC}}$
t_{CONV}	Total conversion time (including sampling time)	$f_{\text{ADC}} = 16 \text{ MHz}$	1		24.75	μs
			4 to 384 (sampling phase) + 12 (successive approximation)			$1/f_{\text{ADC}}$
C_{ADC}	Internal sample and hold capacitor	Direct channels		16		pF
		Multiplexed channels				

Table 52. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{TRIG}	External trigger frequency Regular sequencer	12-bit conversions			$T_{\text{conv}}+1$	$1/f_{\text{ADC}}$
		6/8/10-bit conversions			T_{conv}	$1/f_{\text{ADC}}$
f_{TRIG}	External trigger frequency Injected sequencer	12-bit conversions			$T_{\text{conv}}+2$	$1/f_{\text{ADC}}$
		6/8/10-bit conversions			$T_{\text{conv}}+1$	$1/f_{\text{ADC}}$
R_{AIN}	External input impedance				50	$\text{k}\Omega$
t_{lat}	Injection trigger conversion latency	$f_{\text{ADC}} = 16 \text{ MHz}$	219		281	ns
			3.5		4.5	$1/f_{\text{ADC}}$
t_{latr}	Regular trigger conversion latency	$f_{\text{ADC}} = 16 \text{ MHz}$	156		219	ns
			2.5		3.5	$1/f_{\text{ADC}}$
t_{STAB}	Power-up time				3.5	μs

1. The current consumption through VDDA is composed of two parameters:

- one constant (max 1300 μA)
- one variable (max 400 μA), only during sampling time + 2 first conversion pulses.

So, peak consumption is $1300+400 = 1700 \mu\text{A}$ and average consumption is $1300 + [(4 \text{ sampling} + 2) / 16] \times 400 = 1450 \mu\text{A}$ at 1Msps

2. V_{SSA} must be tied to ground.

Table 53. ADC accuracy⁽¹⁾⁽²⁾

Symbol	Parameter	Test conditions	Min ⁽³⁾	Typ	Max ⁽³⁾	Unit
ET	Total unadjusted error	$2.4 \text{ V} \leq V_{\text{DDA}} \leq 3.6 \text{ V}$ $f_{\text{ADC}} = 8 \text{ MHz}$, $R_{\text{AIN}} = 50 \Omega$ $T_{\text{A}} = -40 \text{ to } 85 \text{ }^\circ\text{C}$	-	2	4	LSB
EO	Offset error		-	1	2	
EG	Gain error		-	1.5	3.5	
ED	Differential linearity error		-	1	2	
EL	Integral linearity error		-	1.7	3	
ENOB	Effective number of bits	$2.4 \text{ V} \leq V_{\text{DDA}} \leq 3.6 \text{ V}$ $f_{\text{ADC}} = 16 \text{ MHz}$, $R_{\text{AIN}} = 50 \Omega$ $T_{\text{A}} = -40 \text{ to } 85 \text{ }^\circ\text{C}$ $1 \text{ kHz} \leq F_{\text{input}} \leq 100 \text{ kHz}$	9.2	10	-	bits
SINAD	Signal-to-noise and distorsion ratio		57.5	62	-	dB
SNR	Signal-to-noise ratio		57.5	62	-	
THD	Total harmonic distorsion		-74	-75	-	
ET	Total unadjusted error	$1.8 \text{ V} \leq V_{\text{DDA}} \leq 2.4 \text{ V}$ $f_{\text{ADC}} = 4 \text{ MHz}$, $R_{\text{AIN}} = 50 \Omega$ $T_{\text{A}} = -40 \text{ to } 85 \text{ }^\circ\text{C}$		2	3	LSB
EO	Offset error			1	1.5	
EG	Gain error			1.5	2	
ED	Differential linearity error			1	2	
EL	Integral linearity error			1	1.5	

1. ADC DC accuracy values are measured after internal calibration.

2. ADC accuracy vs. negative injection current: Injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents. Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in [Section 6.3.11](#) does not affect the ADC accuracy.
3. Based on characterization, not tested in production.

Figure 21. ADC accuracy characteristics

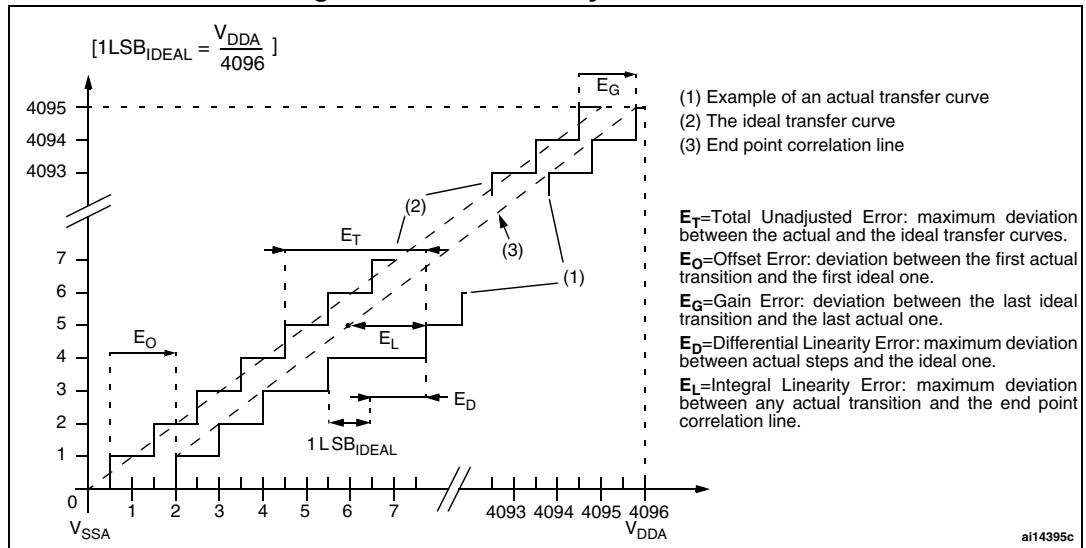
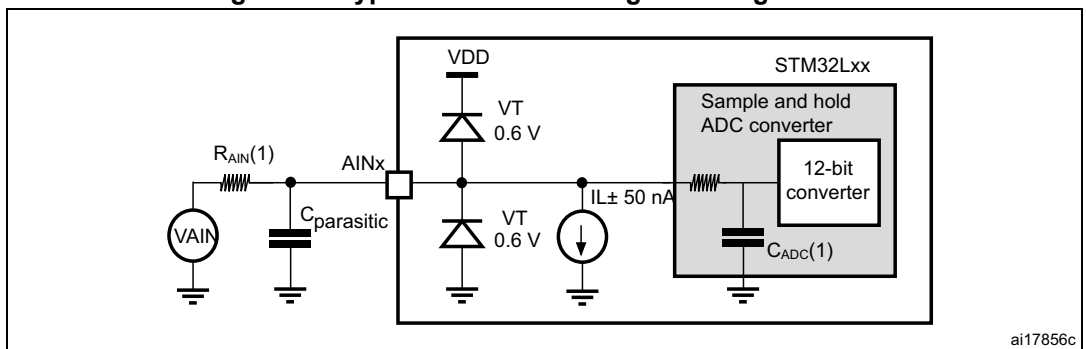
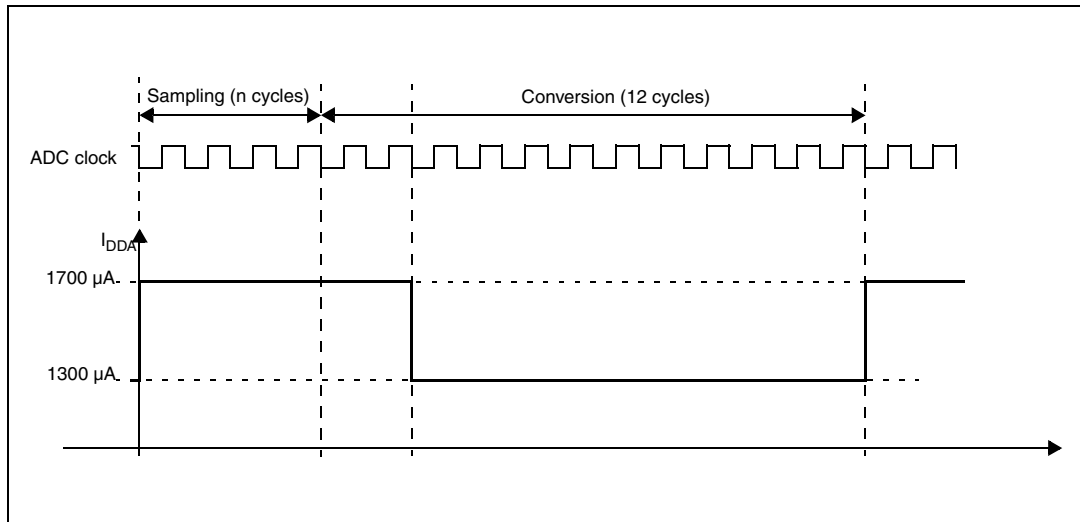


Figure 22. Typical connection diagram using the ADC



1. Refer to [Table 54: RAIN max for fADC = 16 MHz](#) for the value of RAIN and [Table 52: ADC characteristics](#) for the value of CADC
2. $C_{\text{parasitic}}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{\text{parasitic}}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

Figure 23. Maximum dynamic current consumption on V_{DDA} supply pin during ADC conversion**Table 54. R_{AIN} max for $f_{ADC} = 16 \text{ MHz}^{(1)}$**

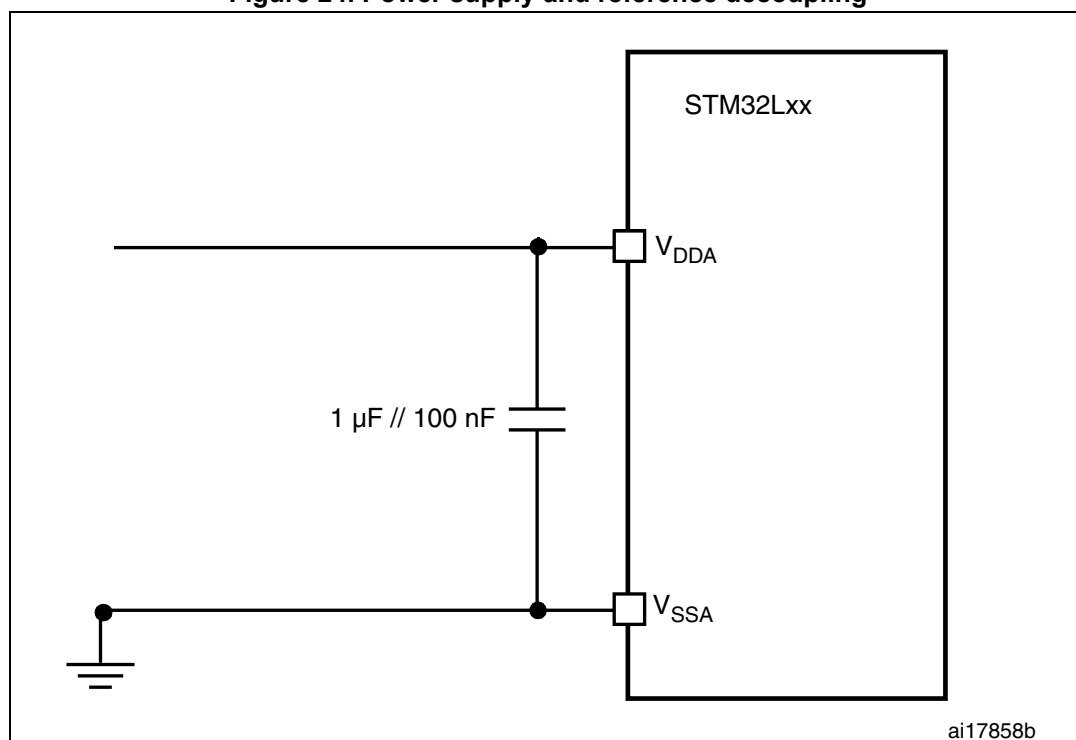
Ts (cycles)	Ts (μs)	R_{AIN} max (kohm)			
		Multiplexed channels		Direct channels	
		$2.4 \text{ V} < V_{DDA} < 3.6 \text{ V}$	$1.8 \text{ V} < V_{DDA} < 2.4 \text{ V}$	$2.4 \text{ V} < V_{DDA} < 3.3 \text{ V}$	$1.8 \text{ V} < V_{DDA} < 2.4 \text{ V}$
4	0.25	Not allowed	Not allowed	0.7	Not allowed
9	0.5625	0.8	Not allowed	2.0	1.0
16	1	2.0	0.8	4.0	3.0
24	1.5	3.0	1.8	6.0	4.5
48	3	6.8	4.0	15.0	10.0
96	6	15.0	10.0	30.0	20.0
192	12	32.0	25.0	50.0	40.0
384	24	50.0	50.0	50.0	50.0

1. Guaranteed by design, not tested in production.

General PCB design guidelines

Power supply decoupling should be performed as shown in the following figure. The 10 nF capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

Figure 24. Power supply and reference decoupling



6.3.17 DAC electrical specifications

Data guaranteed by design, not tested in production, unless otherwise specified.

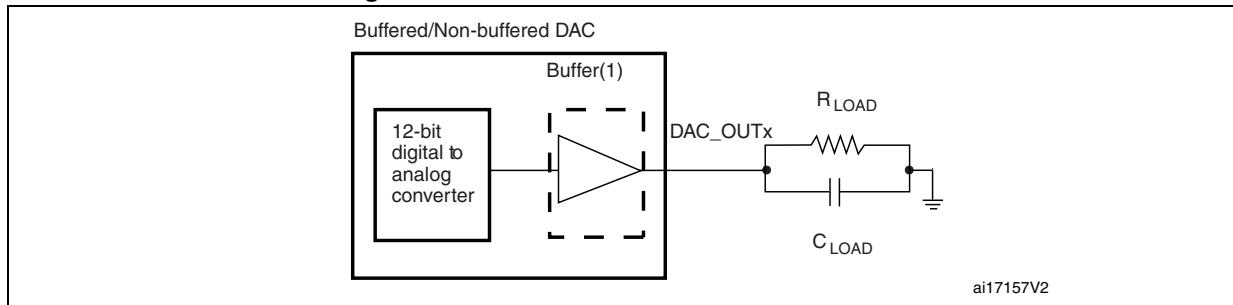
Table 55. DAC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage		1.8		3.6	V
$I_{DDA}^{(1)}$	Current consumption on V_{DDA} supply $V_{DDA} = 3.3\text{ V}$	No load, middle code (0x800)		350	540	μA
		No load, worst code (0xF1C)		540	870	μA
$R_L^{(2)}$	Resistive load	DAC output buffer ON	5			$\text{k}\Omega$
$C_L^{(2)}$	Capacitive load				50	pF
R_O	Output impedance	DAC output buffer OFF	6	8	10	$\text{k}\Omega$
V_{DAC_OUT}	Voltage on DAC_OUT output	DAC output buffer ON	0.2		$V_{DDA} - 0.2$	V
		DAC output buffer OFF	0.5		$V_{DDA} - 1\text{LSB}$	mV
$DNL^{(1)}$	Differential non linearity ⁽³⁾	$C_L \leq 50\text{ pF}$, $R_L \geq 5\text{ k}\Omega$ DAC output buffer ON		1.5	3	LSB
		No R_{LOAD} , $C_L \leq 50\text{ pF}$ DAC output buffer OFF		1.5	3	
$INL^{(1)}$	Integral non linearity ⁽⁴⁾	$C_L \leq 50\text{ pF}$, $R_L \geq 5\text{ k}\Omega$ DAC output buffer ON		2	4	
		No R_{LOAD} , $C_L \leq 50\text{ pF}$ DAC output buffer OFF		2	4	
Offset ⁽¹⁾	Offset error at code 0x800 ⁽⁵⁾	$C_L \leq 50\text{ pF}$, $R_L \geq 5\text{ k}\Omega$ DAC output buffer ON		± 10	± 25	
		No R_{LOAD} , $C_L \leq 50\text{ pF}$ DAC output buffer OFF		± 5	± 8	
Offset1 ⁽¹⁾	Offset error at code 0x001 ⁽⁶⁾	No R_{LOAD} , $C_L \leq 50\text{ pF}$ DAC output buffer OFF		± 1.5	± 5	
$d\text{Offset}/dT^{(1)}$	Offset error temperature coefficient (code 0x800)	$V_{DDA} = 3.3\text{ V}$ $T_A = 0\text{ to }50\text{ }^\circ\text{C}$ DAC output buffer OFF	-20	-10	0	$\mu\text{V}/^\circ\text{C}$
		$V_{DDA} = 3.3\text{ V}$ $T_A = 0\text{ to }50\text{ }^\circ\text{C}$ DAC output buffer ON	0	20	50	

Table 55. DAC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Gain ⁽¹⁾	Gain error ⁽⁷⁾	$C_L \leq 50 \text{ pF}$, $R_L \geq 5 \text{ k}\Omega$ DAC output buffer ON		+0.1 / -0.2%	+0.2 / -0.5%	%
		No R_{LOAD} , $C_L \leq 50 \text{ pF}$ DAC output buffer OFF		+0 / -0.2%	+0 / -0.4%	
dGain/dT ⁽¹⁾	Gain error temperature coefficient	$V_{DDA} = 3.3\text{V}$ $T_A = 0 \text{ to } 50 \text{ }^\circ\text{C}$ DAC output buffer OFF	-10	-2	0	$\mu\text{V}/^\circ\text{C}$
		$V_{DDA} = 3.3\text{V}$ $T_A = 0 \text{ to } 50 \text{ }^\circ\text{C}$ DAC output buffer ON	-40	-8	0	
TUE ⁽¹⁾	Total unadjusted error	$C_L \leq 50 \text{ pF}$, $R_L \geq 5 \text{ k}\Omega$ DAC output buffer ON		12	30	LSB
		No R_{LOAD} , $C_L \leq 50 \text{ pF}$ DAC output buffer OFF		8	12	
t _{SETTLING}	Settling time (full scale: for a 12-bit code transition between the lowest and the highest input codes till DAC_OUT reaches final value $\pm 1\text{LSB}$)	$C_L \leq 50 \text{ pF}$, $R_L \geq 5 \text{ k}\Omega$		7	12	μs
Update rate	Max frequency for a correct DAC_OUT change (95% of final value) with 1 LSB variation in the input code	$C_L \leq 50 \text{ pF}$, $R_L \geq 5 \text{ k}\Omega$			1	Msp/s
t _{WAKEUP}	Wakeup time from off state (setting the ENx bit in the DAC Control register) ⁽⁸⁾	$C_L \leq 50 \text{ pF}$, $R_L \geq 5 \text{ k}\Omega$		9	15	μs
PSRR+	V_{DDA} supply rejection ratio (static DC measurement)	$C_L \leq 50 \text{ pF}$, $R_L \geq 5 \text{ k}\Omega$		-60	-35	dB

1. Data based on characterization results.
2. Connected between DAC_OUT and V_{SSA} .
3. Difference between two consecutive codes - 1 LSB.
4. Difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 4095.
5. Difference between the value measured at Code (0x800) and the ideal value = $V_{DDA}/2$.
6. Difference between the value measured at Code (0x001) and the ideal value.
7. Difference between ideal slope of the transfer function and measured slope computed from code 0x000 and 0xFFFF when buffer is OFF, and from code giving 0.2 V and $(V_{DDA} - 0.2) \text{ V}$ when buffer is ON.
8. In buffered mode, the output can overshoot above the final value for low input code (starting from min value).

Figure 25. 12-bit buffered /non-buffered DAC

1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

6.3.18 Comparator

Table 56. Comparator 1

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
V _{DDA}	Analog supply voltage		1.8		3.6	V
R _{400K}	R _{400K} value			400		kΩ
R _{10K}	R _{10K} value			10		
V _{IN}	Comparator 1 input voltage range		0.6		V _{DDA}	V
t _{START}	Comparator startup time			7	10	μs
t _d	Propagation delay ⁽²⁾			3	10	
V _{offset}	Comparator offset			±3	±10	mV
dV _{offset} /dt	Comparator offset variation in worst voltage stress conditions	V _{DDA} = 3.6 V V _{IN+} = 0 V V _{IN-} = V _{REFINT} T _A = 25 °C	0	1.5	10	mV/1000 h
I _{COMP1}	Current consumption ⁽³⁾			160	260	nA

1. Based on characterization, not tested in production.

2. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.

3. Comparator consumption only. Internal reference voltage not included.

Table 57. Comparator 2 characteristics

Symbol	Parameter	Conditions	Min	Typ	Max ⁽¹⁾	Unit
V_{DDA}	Analog supply voltage		1.8		3.6	V
V_{IN}	Comparator 2 input voltage range		0		V_{DDA}	V
t_{START}	Comparator startup time	Fast mode		15	20	μs
		Slow mode		20	25	
$t_{d\ slow}$	Propagation delay ⁽²⁾ in slow mode	$1.8\ V \leq V_{DDA} \leq 2.7\ V$		1.8	3.5	
		$2.7\ V \leq V_{DDA} \leq 3.6\ V$		2.5	6	
$t_{d\ fast}$	Propagation delay ⁽²⁾ in fast mode	$1.8\ V \leq V_{DDA} \leq 2.7\ V$		0.8	2	
		$2.7\ V \leq V_{DDA} \leq 3.6\ V$		1.2	4	
V_{offset}	Comparator offset error			± 4	± 20	mV
$dThreshold/dt$	Threshold voltage temperature coefficient	$V_{DDA} = 3.3V$ $T_A = 0\ to\ 50\ ^\circ C$ $V_- = V_{REFINT},\ 3/4\ V_{REF+},\ 1/2\ V_{REFINT},\ 1/4\ V_{REFINT}$		15	30	ppm/ $^\circ C$
I_{COMP2}	Current consumption ⁽³⁾	Fast mode		3.5	5	μA
		Slow mode		0.5	2	

1. Based on characterization, not tested in production.
2. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.
3. Comparator consumption only. Internal reference voltage (necessary for comparator operation) is not included.

6.3.19 LCD controller

The STM32L100xx embeds a built-in step-up converter to provide a constant LCD reference voltage independently from the V_{DD} voltage. An external capacitor C_{ext} must be connected to the V_{LCD} pin to decouple this converter.

Table 58. LCD controller characteristics

Symbol	Parameter	Min	Typ	Max	Unit
V_{LCD}	LCD external voltage			3.6	V
V_{LCD0}	LCD internal reference voltage 0		2.6		
V_{LCD1}	LCD internal reference voltage 1		2.73		
V_{LCD2}	LCD internal reference voltage 2		2.86		
V_{LCD3}	LCD internal reference voltage 3		2.98		
V_{LCD4}	LCD internal reference voltage 4		3.12		
V_{LCD5}	LCD internal reference voltage 5		3.26		
V_{LCD6}	LCD internal reference voltage 6		3.4		
V_{LCD7}	LCD internal reference voltage 7		3.55		
C_{ext}	V_{LCD} external capacitance	0.1		2	μF
$I_{LCD}^{(1)}$	Supply current at $V_{DD} = 2.2 V$		3.3		μA
	Supply current at $V_{DD} = 3.0 V$		3.1		
$R_{Htot}^{(2)}$	Low drive resistive network overall value	5.28	6.6	7.92	$M\Omega$
$R_L^{(2)}$	High drive resistive network total value	192	240	288	$k\Omega$
V_{44}	Segment/Common highest level voltage			V_{LCD}	V
V_{34}	Segment/Common 3/4 level voltage		$3/4 V_{LCD}$		V
V_{23}	Segment/Common 2/3 level voltage		$2/3 V_{LCD}$		
V_{12}	Segment/Common 1/2 level voltage		$1/2 V_{LCD}$		
V_{13}	Segment/Common 1/3 level voltage		$1/3 V_{LCD}$		
V_{14}	Segment/Common 1/4 level voltage		$1/4 V_{LCD}$		
V_0	Segment/Common lowest level voltage	0			
$\Delta V_{xx}^{(3)}$	Segment/Common level voltage error $T_A = -40$ to $85^\circ C$			± 50	mV

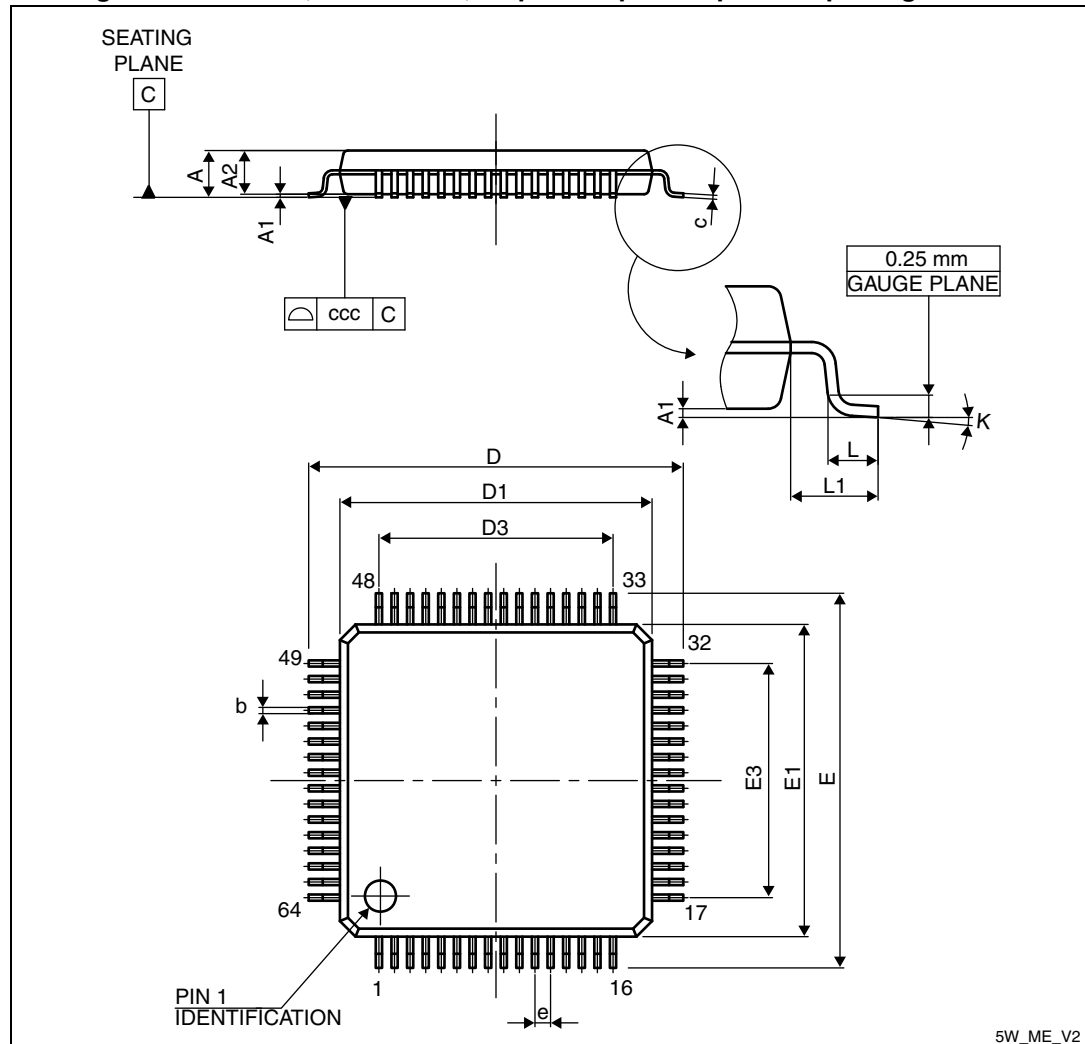
1. LCD enabled with 3 V internal step-up active, 1/8 duty, 1/4 bias, division ratio= 64, all pixels active, no LCD connected
2. Guaranteed by design, not tested in production.
3. Based on characterization, not tested in production.

7 Package characteristics

7.1 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Figure 26. LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package outline



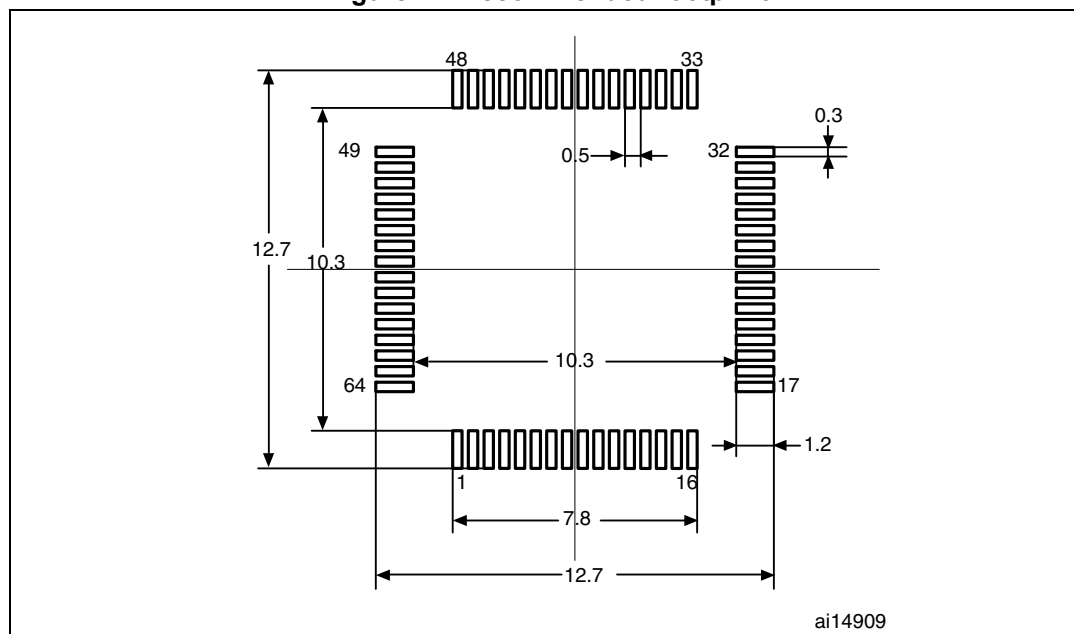
1. Drawing is not to scale.

Table 59. LQFP64, 10 x 10 mm 64-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A			1.600			0.0630
A1		0.050	0.150		0.0020	0.0059
A2	1.400	1.350	1.450	0.0551	0.0531	0.0571
b	0.220	0.170	0.270	0.0087	0.0067	0.0106
c		0.090	0.200		0.0035	0.0079
D	12.000	11.800	12.200	0.4724	0.4646	0.4803
D1	10.000	9.800	10.200	0.3937	0.3858	0.4016
D3	7.500			0.2953		
E	12.000	11.800	12.200	0.4724	0.4646	0.4803
E1	10.000	9.800	10.200	0.3937	0.3858	0.4016
E3	7.500			0.2953		
e	0.500			0.0197		
L	0.600	0.450	0.750	0.0236	0.0177	0.0295
L1	1.000			0.0394		
ccc			0.080			0.0031
K	3.5	0.0	7.0	3.5	0.0	7.0

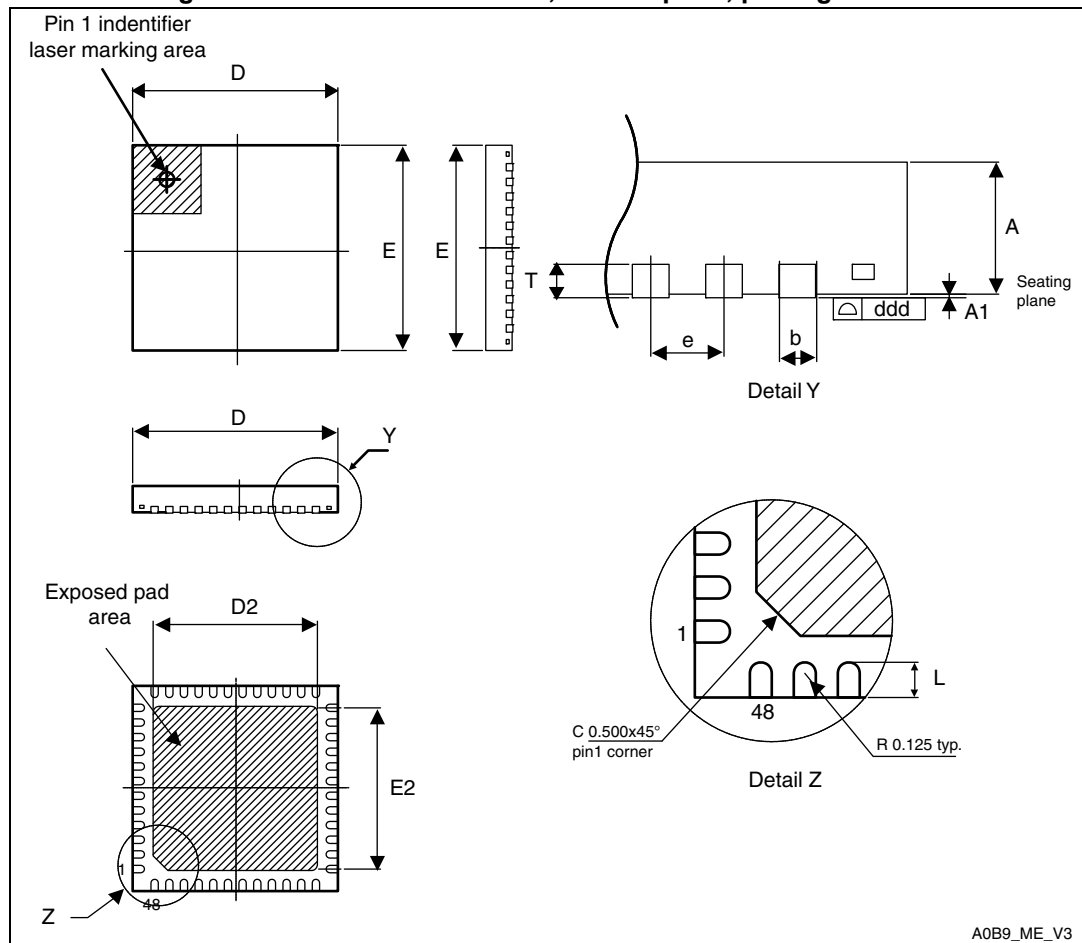
1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 27. Recommended footprint



1. Dimensions are in millimeters.

Figure 28. UFQFPN48 7 x 7 mm, 0.5 mm pitch, package outline



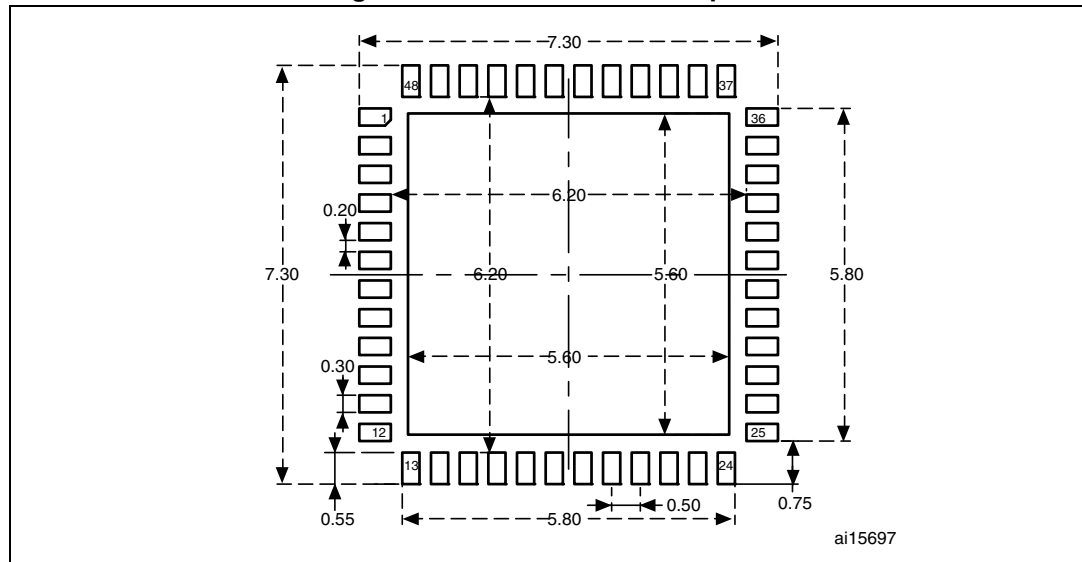
1. Drawing is not to scale.
1. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
1. There is an exposed die pad on the underside of the UFQFPN package. It is recommended to connect and solder this back-side pad to PCB ground.

Table 60. UFQFPN48 7 x 7 mm, 0.5 mm pitch, package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
D	6.900	7.000	7.100	0.2717	0.2756	0.2795
E	6.900	7.000	7.100	0.2717	0.2756	0.2795
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
T		0.152			0.0060	
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
e		0.500			0.0197	

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 29. Recommended footprint



1. Dimensions are in millimeters.

1. Drawing is not to scale.

7.2 Thermal characteristics

The maximum chip-junction temperature, $T_J \text{ max}$, in degrees Celsius, may be calculated using the following equation:

$$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max} \times \Theta_{JA})$$

Where:

- $T_A \text{ max}$ is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- $P_D \text{ max}$ is the sum of $P_{INT} \text{ max}$ and $P_{I/O} \text{ max}$ ($P_D \text{ max} = P_{INT} \text{ max} + P_{I/O} \text{ max}$),
- $P_{INT} \text{ max}$ is the product of I_{DD} and V_{DD} , expressed in Watts. This is the maximum chip internal power.

$P_{I/O} \text{ max}$ represents the maximum power dissipation on output pins where:

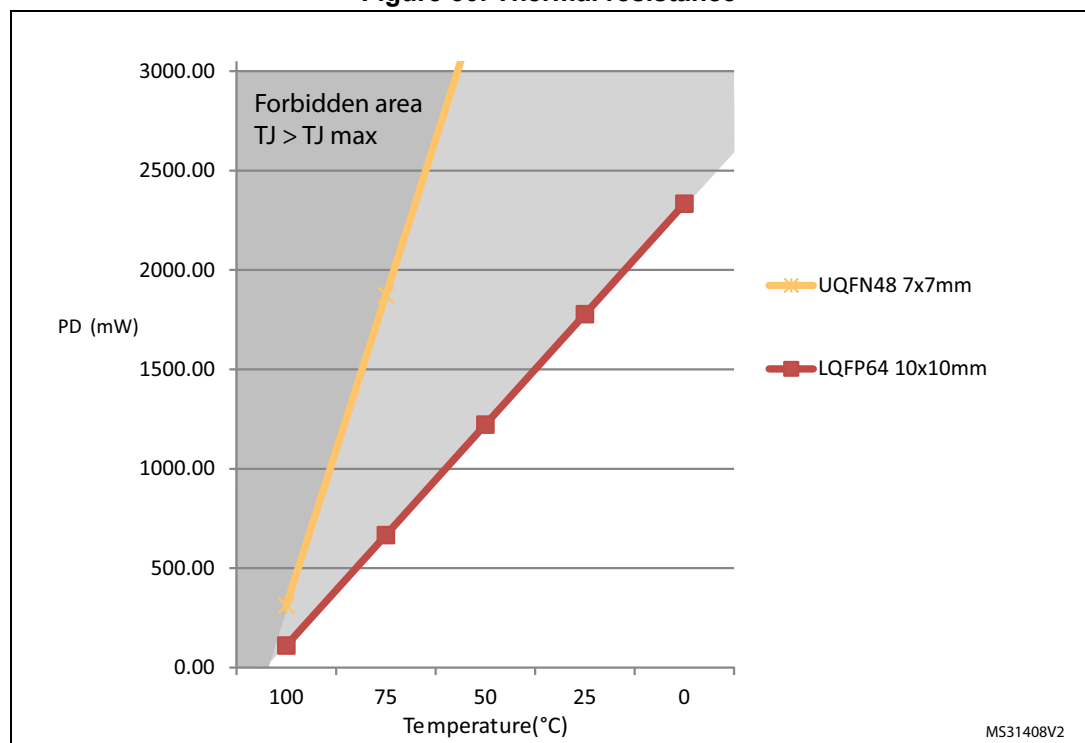
$$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma ((V_{DD} - V_{OH}) \times I_{OH}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 61. Thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal resistance junction-ambient LQFP64 - 10 x 10 mm / 0.5 mm pitch	45	°C/W
	Thermal resistance junction-ambient UFQFPN48 - 7 x 7 mm / 0.5 mm pitch	16	

Figure 30. Thermal resistance



7.2.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

8 Ordering information scheme

Table 62. Ordering information scheme

Example:	STM32	L	100	C	8		T	6	xxx
Device family STM32 = ARM-based 32-bit microcontroller									
Product type L = Low power									
Device subfamily 100: Devices with LCD									
Pin count C = 48 pins R = 64 pins									
Flash memory size 6 = 32 Kbytes of Flash memory 8 = 64 Kbytes of Flash memory B = 128 Kbytes of Flash memory									
Package T = LQFP U = UFQFPN									
Temperature range 6 = Industrial temperature range, -40 to 85 °C									
Packing TR = tape and reel No character = tray or tube									

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.



9 Revision history

Table 63. Document revision history

Date	Revision	Changes
21-Feb-2013	1	Initial release.

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